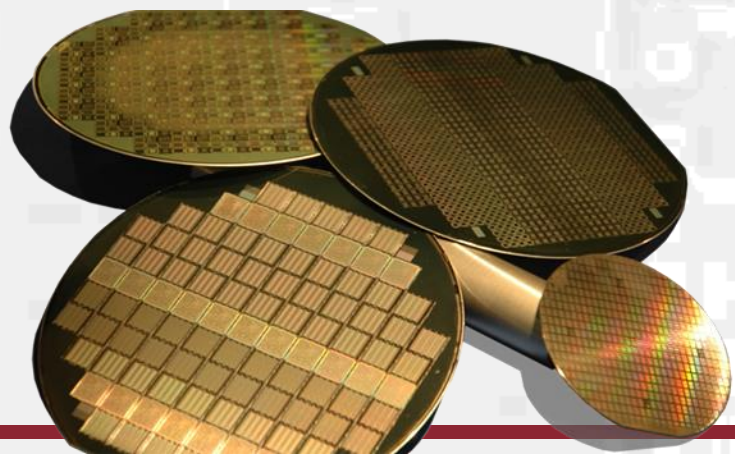




Budapest University of Technology and Economics
Department of Electron Devices

Solar cell working principles

Balázs Plesz



<http://www.eet.bme.hu>

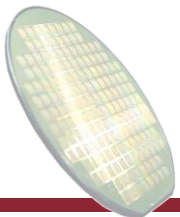
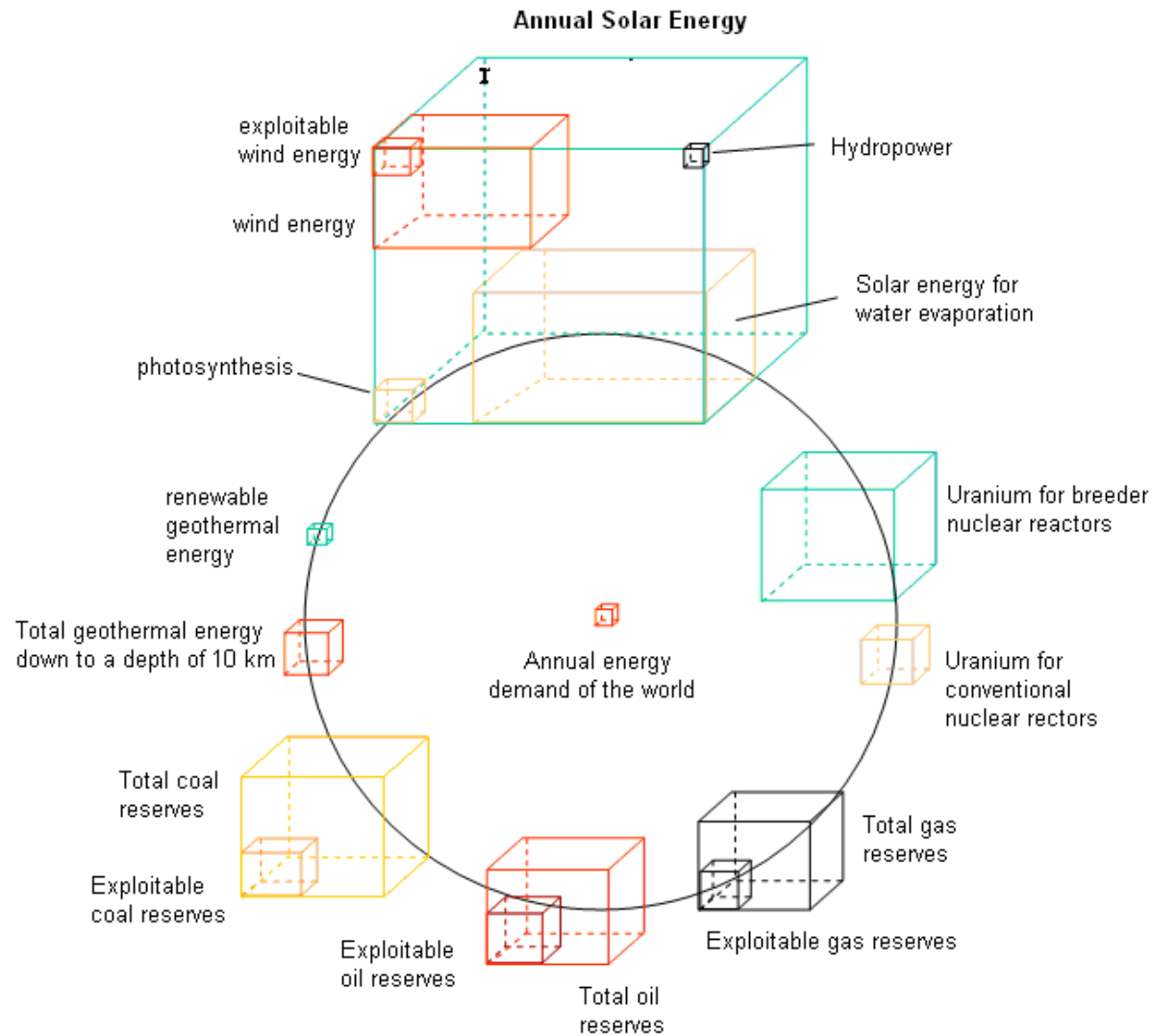


Motto

"One day, a person would no more think about buying a house without solar than they would a house without plumbing."

— Bob Clearman, Dow Chemical



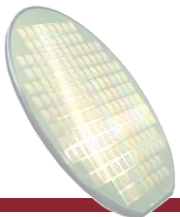




Photovoltaic systems

- ▶ Stand alone or grid connected systems?
 - Reliability
 - Reconsideration of the tasks of the grid
 - A single plant for every user?

- ▶ Tracking or fixed Installation?
 - Higher energy gain with tracking
 - Higher costs
 - Shading
 - Higher maintenance



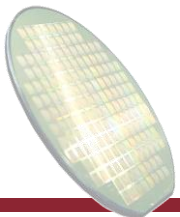


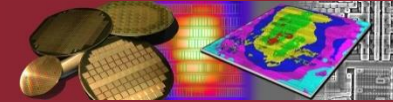
Dilemma of solar cell usage

**High efficiency
solar cells with
concentrators**

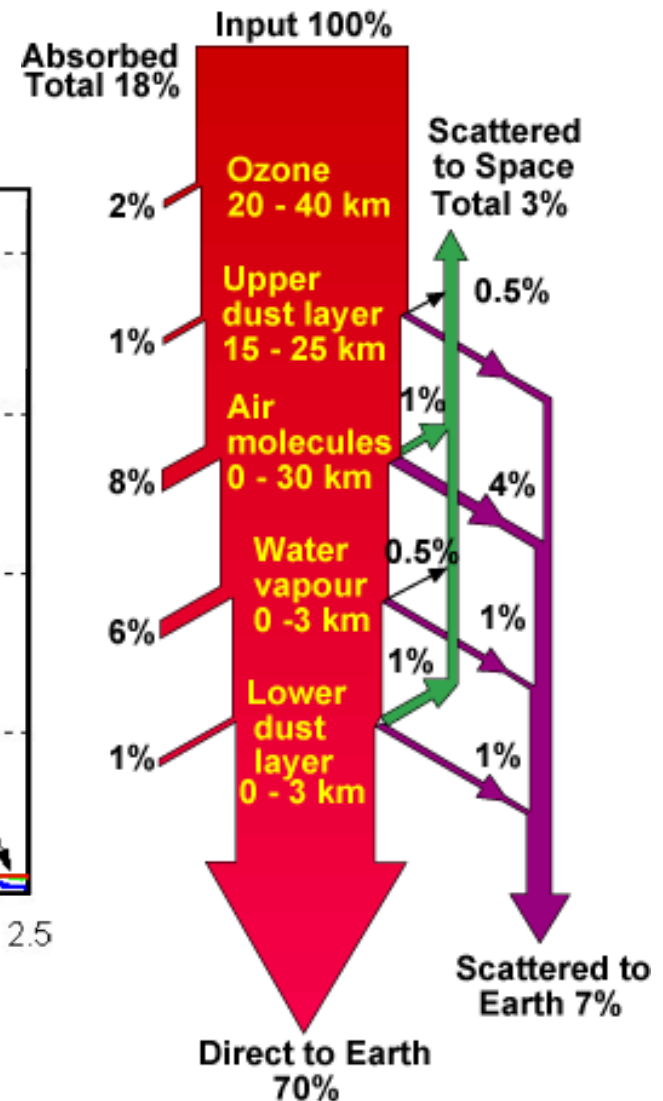
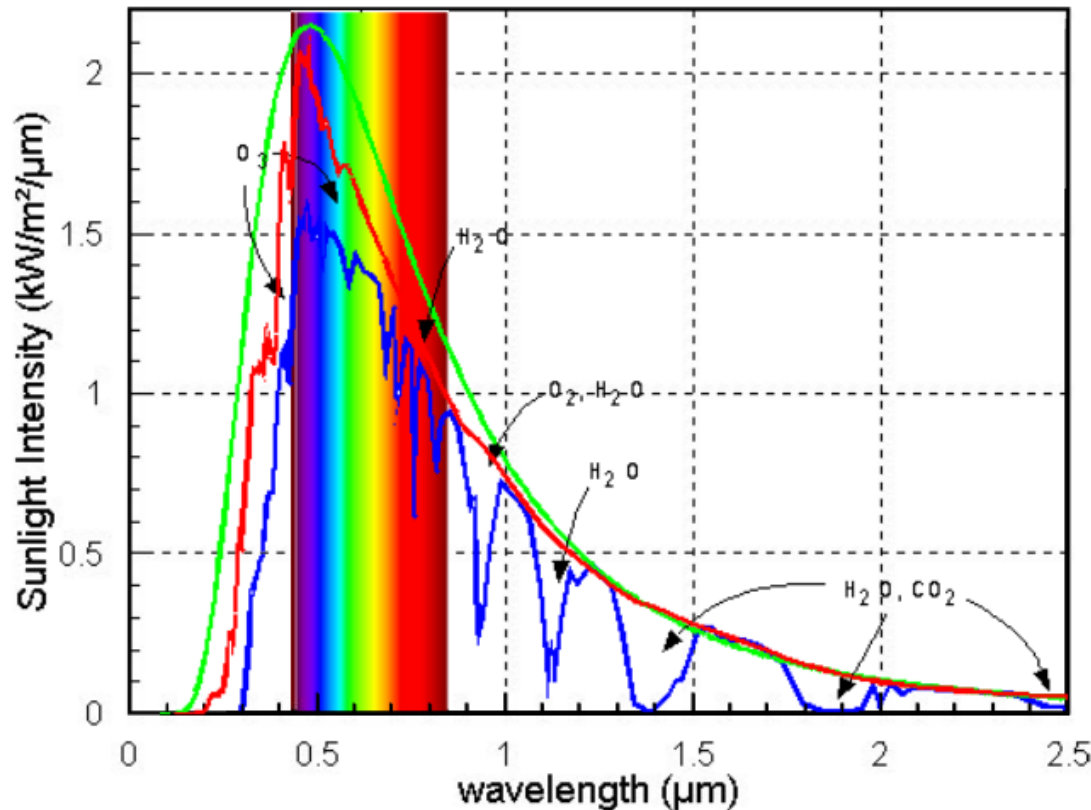


**Large arrays
of low cost
solar cells**

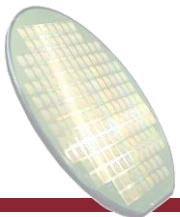
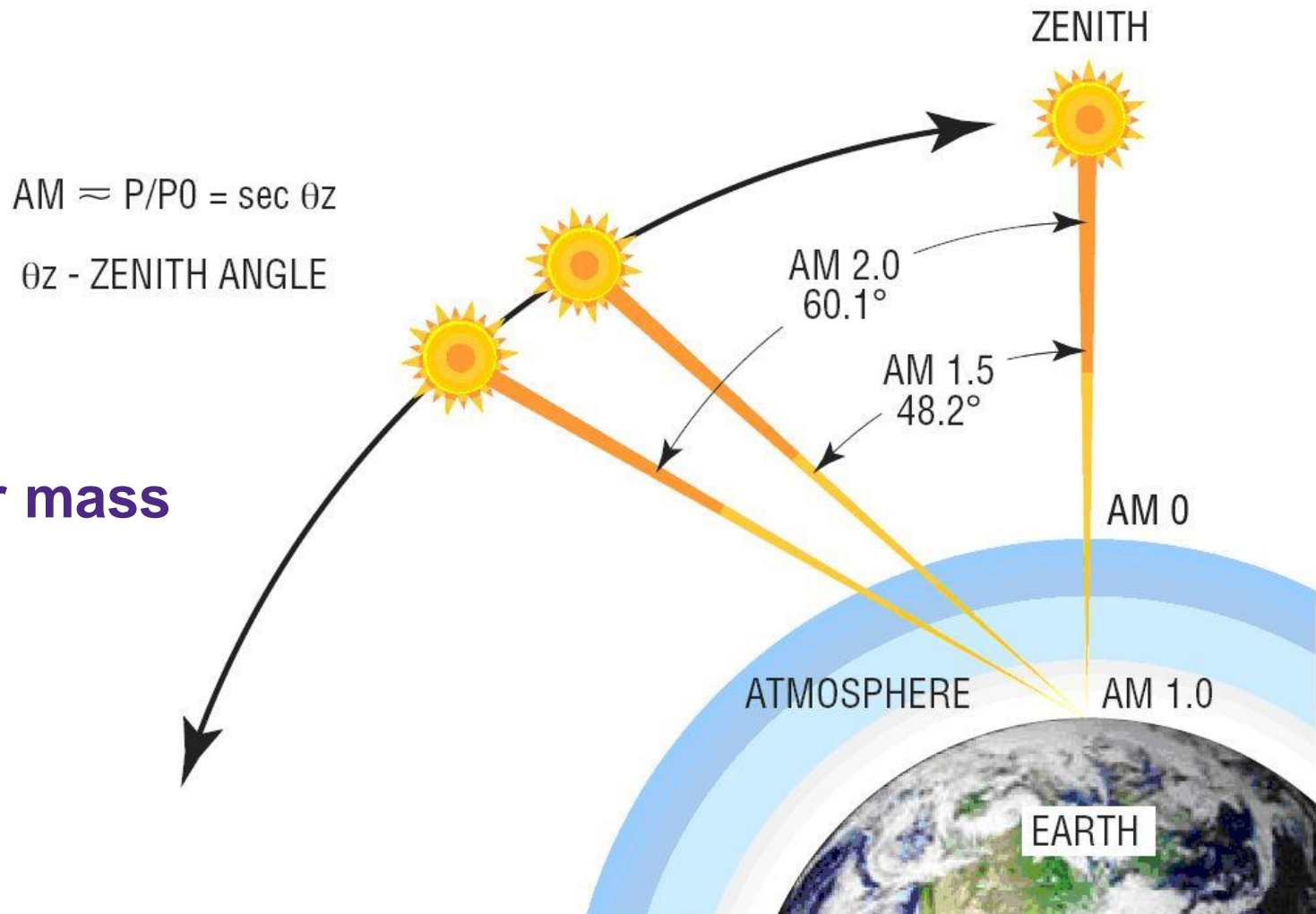




Solar energy properties



Solar radiation on the surface of Earth





HOW DO SOLAR CELLS WORK?





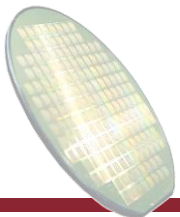
What is a solar cell?

► Definition:

- Solar cells are devices that use the photoelectric effect to convert solar irradiation directly to electrical energy.

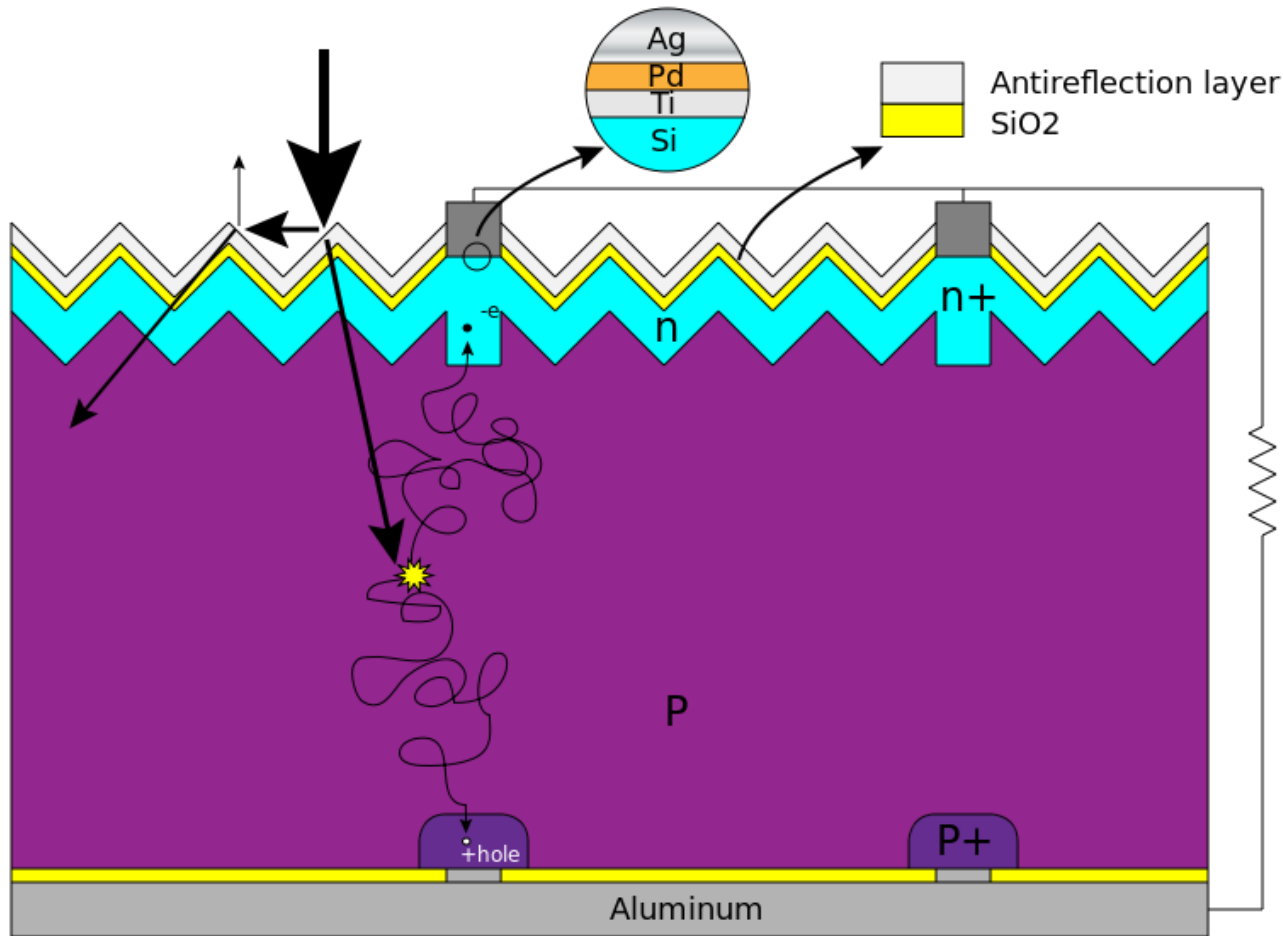
► Practical implementation:

- An illuminated semiconductor diode (p-n junction).





Solar cell basic structure



$$V_{pn} = V_T \ln \frac{N_d N_a}{n_i^2}$$

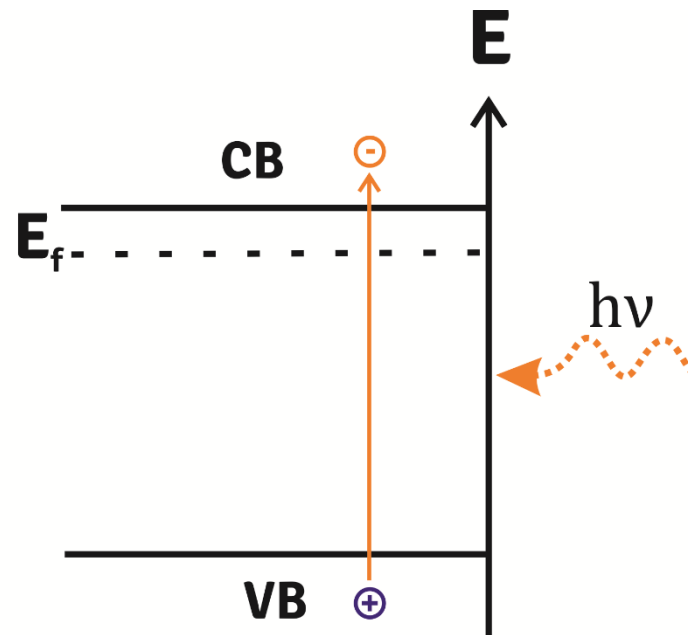


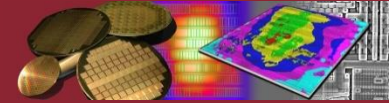


How do solar cells work?

► Photoelectric effect

- Incoming photons excites an electron from the valence to the conduction band (photogeneration)
This happens only if the energy of the photon is higher than the bandgap of the semiconductor ($h\nu > W_g$)

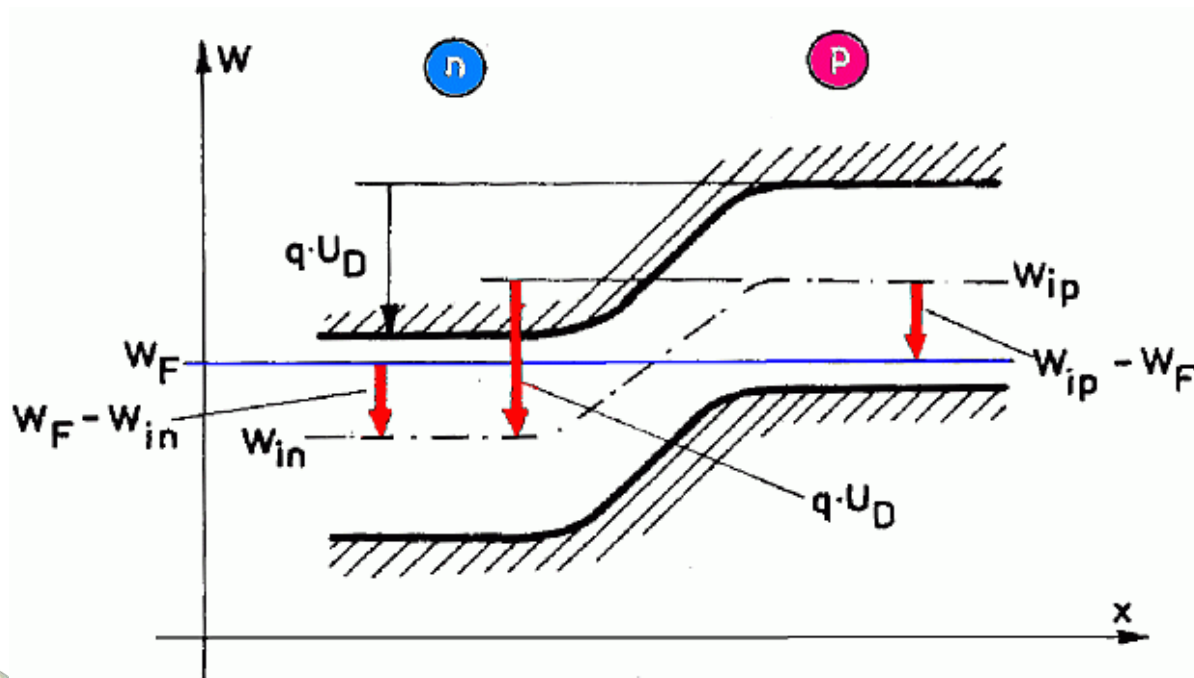




How do solar cells work?

► Built-in electric field

- The different dopings on the two sides of the p-n junction result in an electric field in the depleted region.

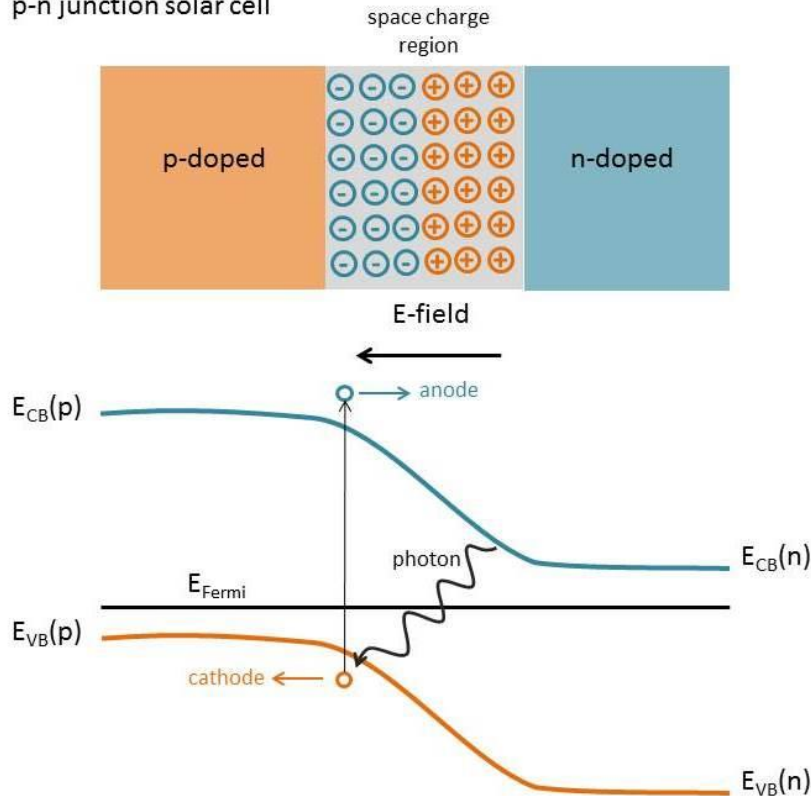


$$U_D = U_T \ln \frac{N_d N_a}{n_i^2}$$

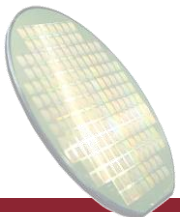


How do solar cells work?

p-n junction solar cell



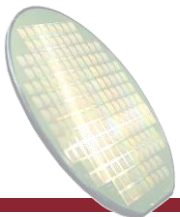
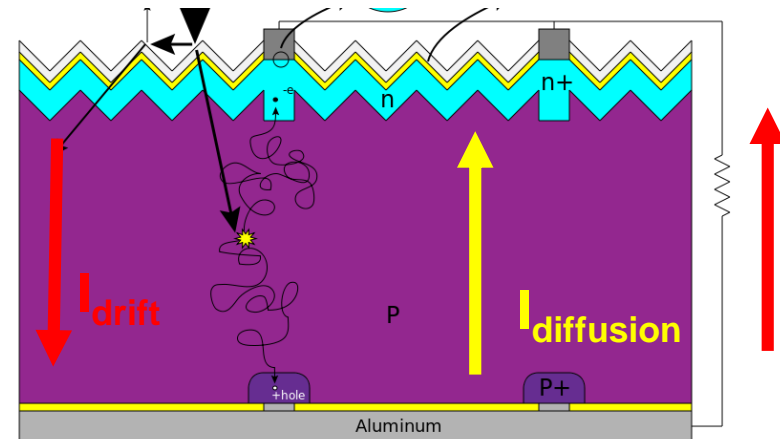
Photon with higher energy than the bandgap excite electron-hole pairs. The built-in potential of the p-n junction separates the charge carriers, and drives the electrons to the n-side and the holes to the p-side (drift current). Thus negative charge accumulates on the n-side and a positive on the p-side.





How do solar cells work?

- ▶ If we put an external resistor between the n-side and the p-side a current will start to flow on this external resistor, and we can extract electrical power.
- ▶ If there is no external resistor, the voltage will rise until the so called open circuit voltage, and due to the diffusion potential of the charge carriers a diffusion current will start to flow in the opposite direction to the drift current.





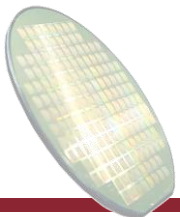
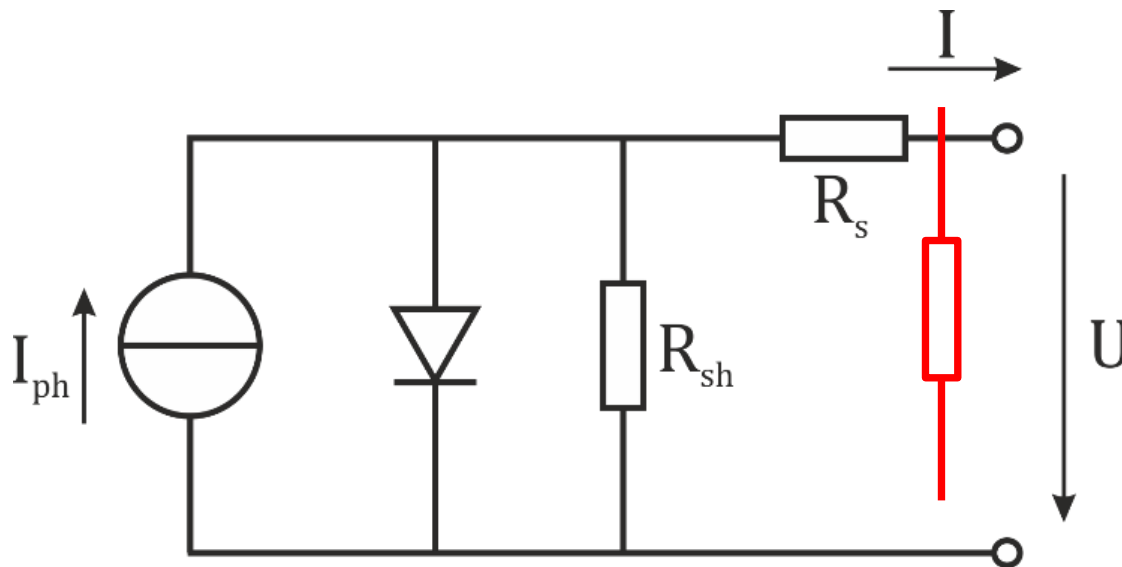
EQUIVALENT CIRCUIT AND I-V CURVE





Equivalent circuit of a solar cell

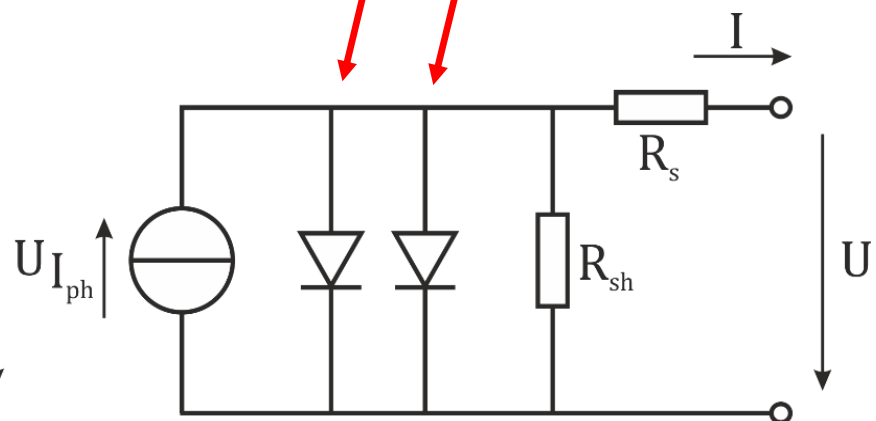
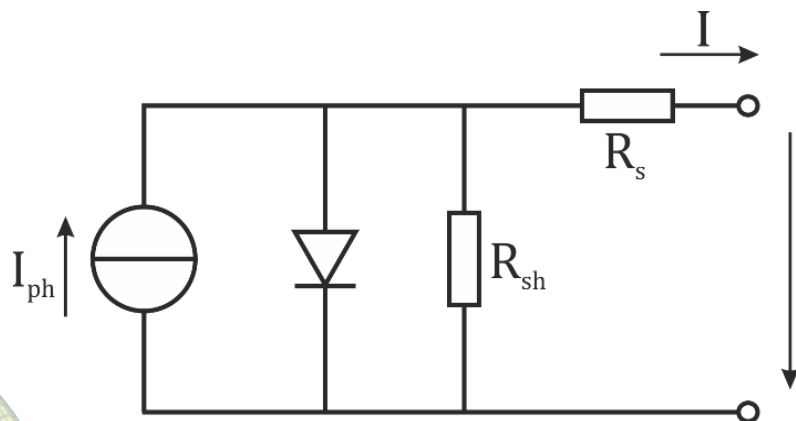
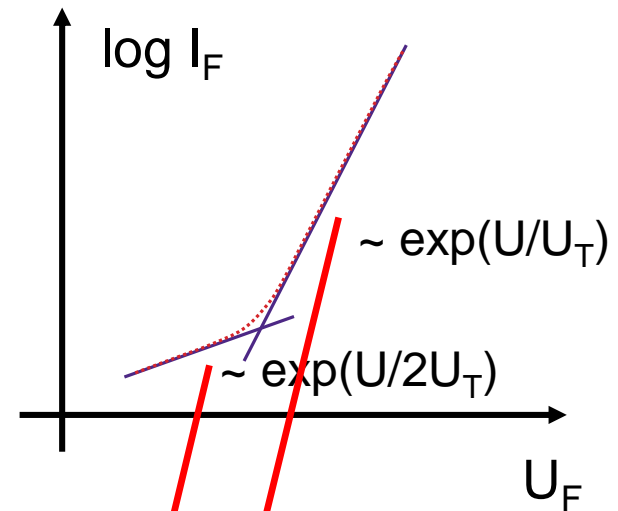
- ▶ Current source: drift current from the photogenerated charge carriers
- ▶ Diode: p-n junction, its current depends on the diffusion potential (forward current = diffusion current)
- ▶ The diffusion potential of the diode is determined by the load resistance and the parasitic resistances





Single diode or two diode model

- Recombination current can be taken into account with a two diode model
- It is neglectable compared to the photo current





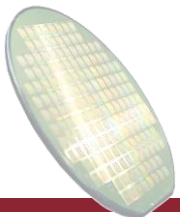
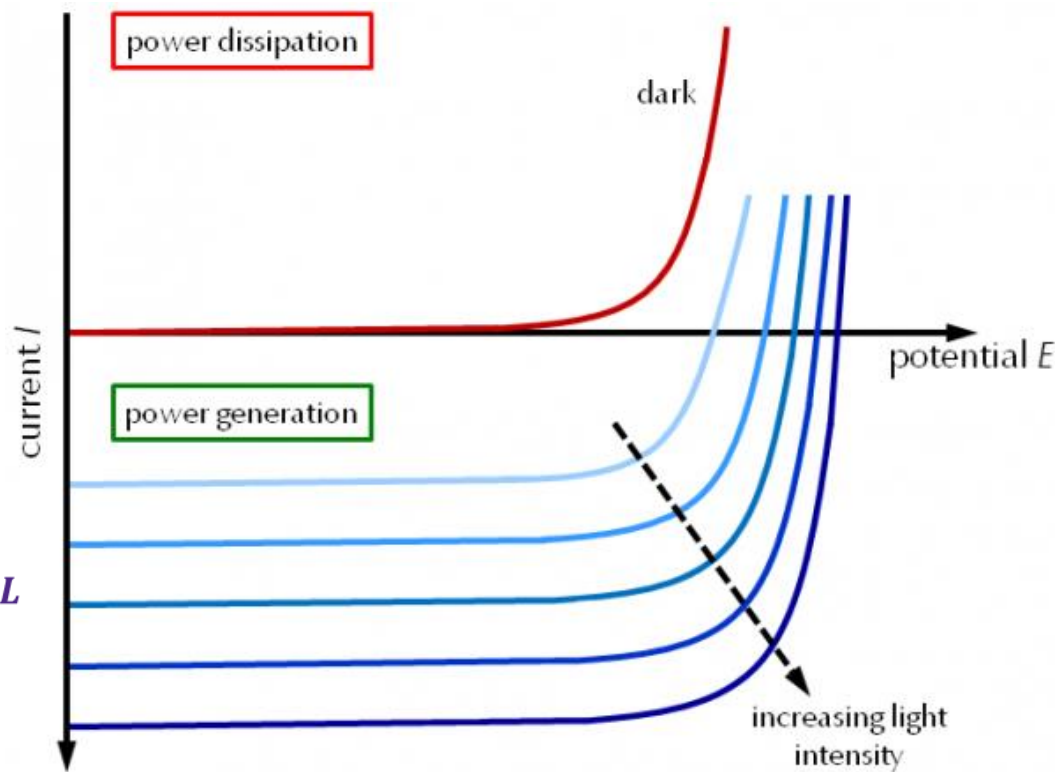
I-V curve of a solar cell

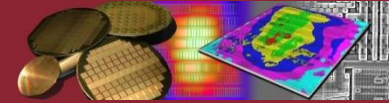
► *Ideal solar cell*

► *Non-ideal solar cell*

► $I = I_0 \left(e^{\frac{U}{\eta U_T}} - 1 \right)$

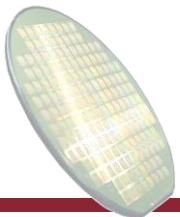
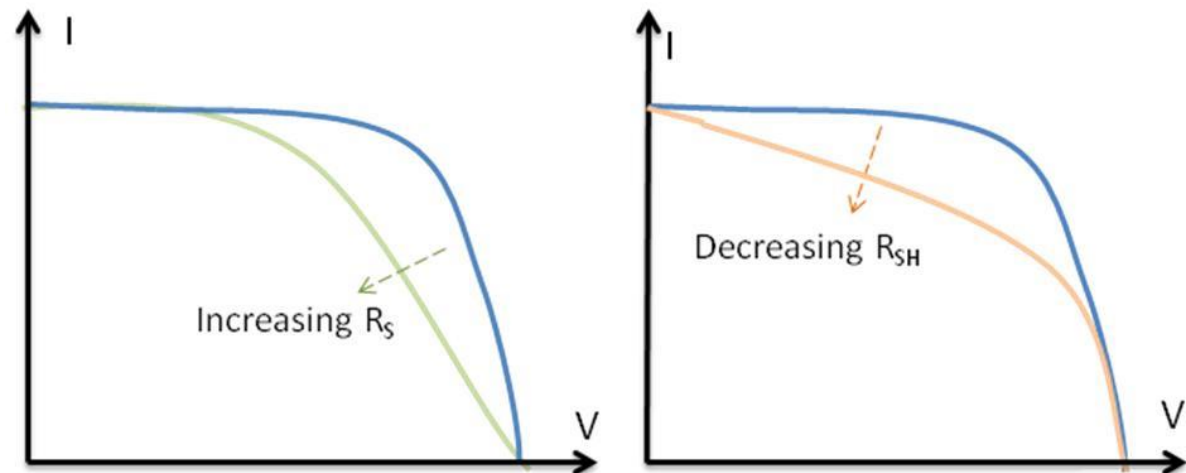
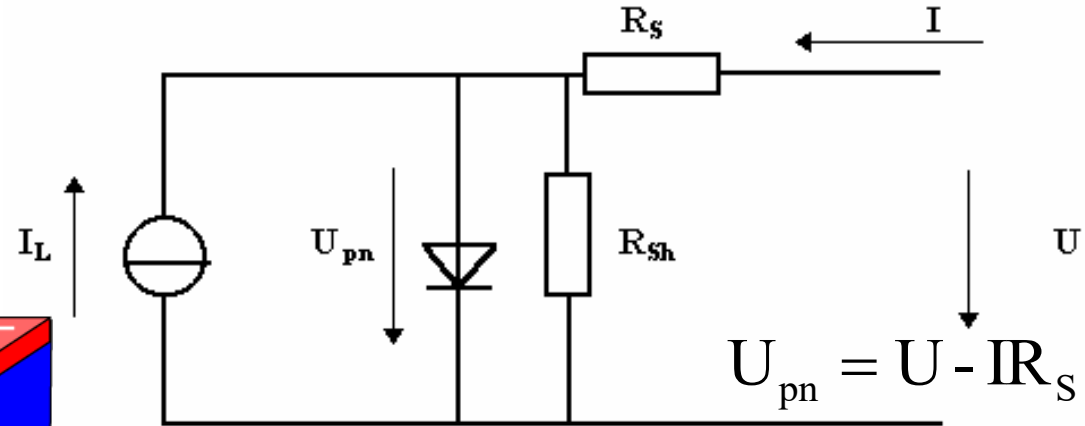
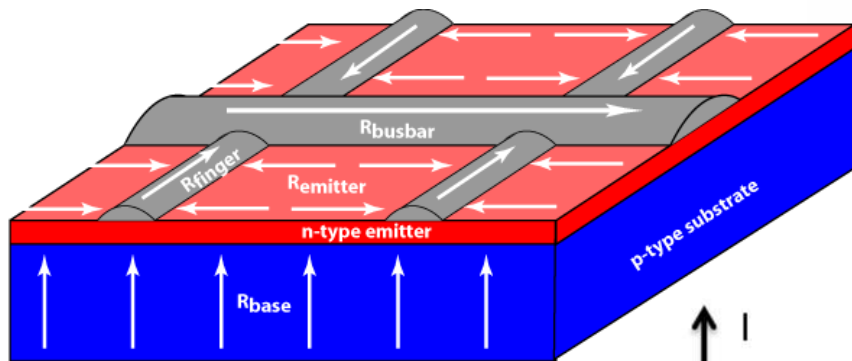
► $I = I_{ph} - I_0 \left(e^{\frac{U+I \cdot R_S}{n U_T}} - 1 \right) - \frac{U+I \cdot R_S}{R_{Sh}}$

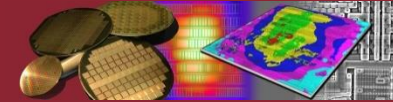




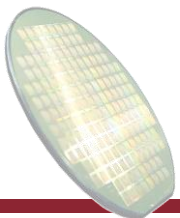
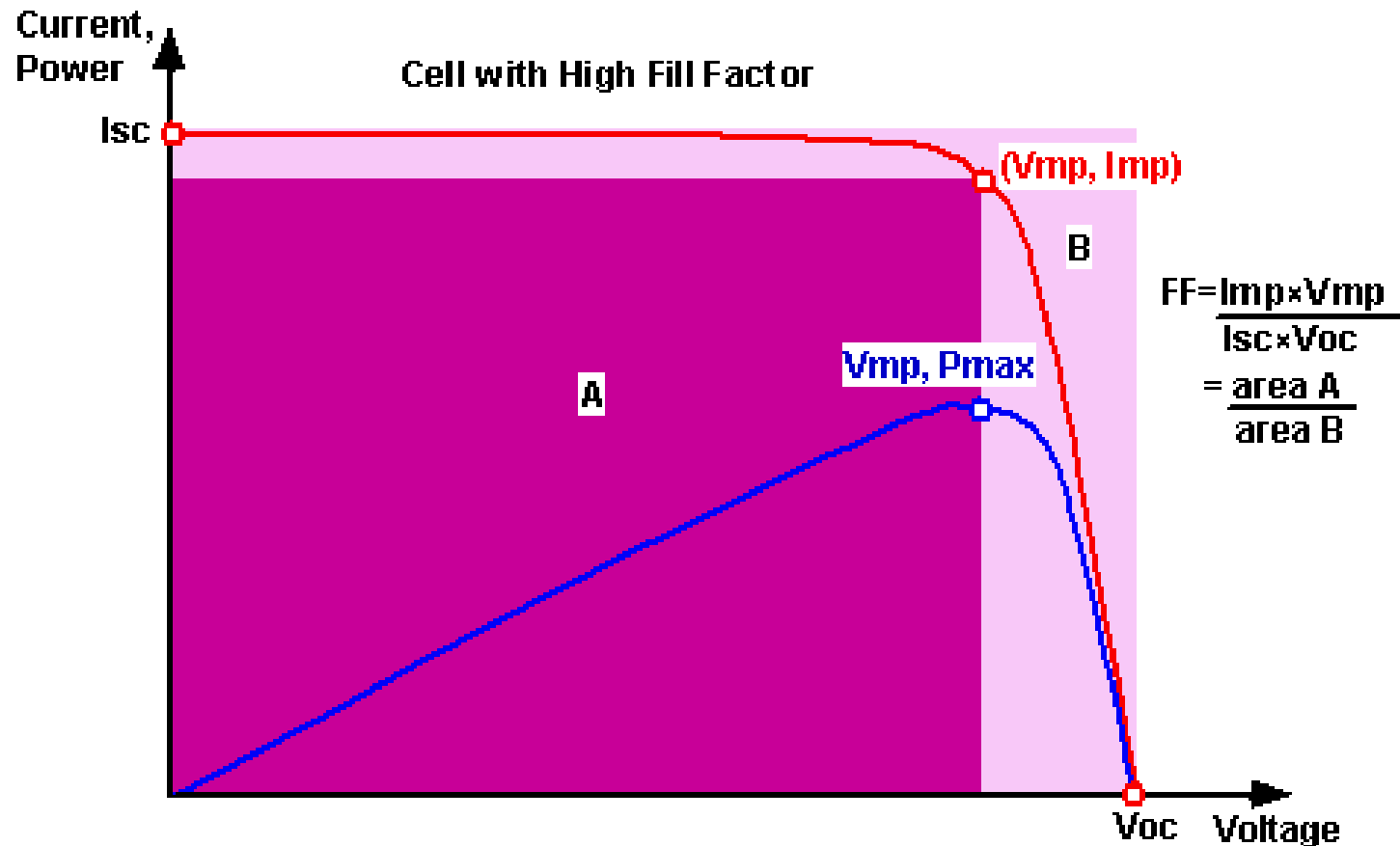
Effect of parasitic resistances

- ▶ R_s – series resistance
- ▶ R_{sh} – shunt resistance
- ▶ I_L – photocurrent





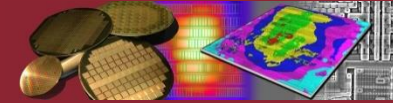
Ideal solar cell characteristics





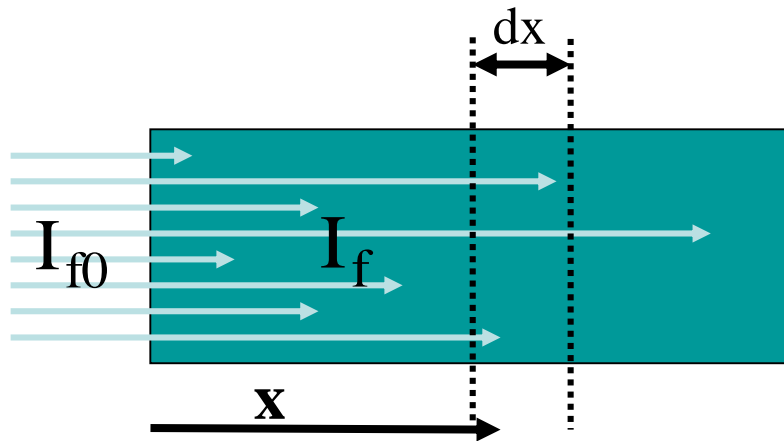
SPECTRAL RESPONSE



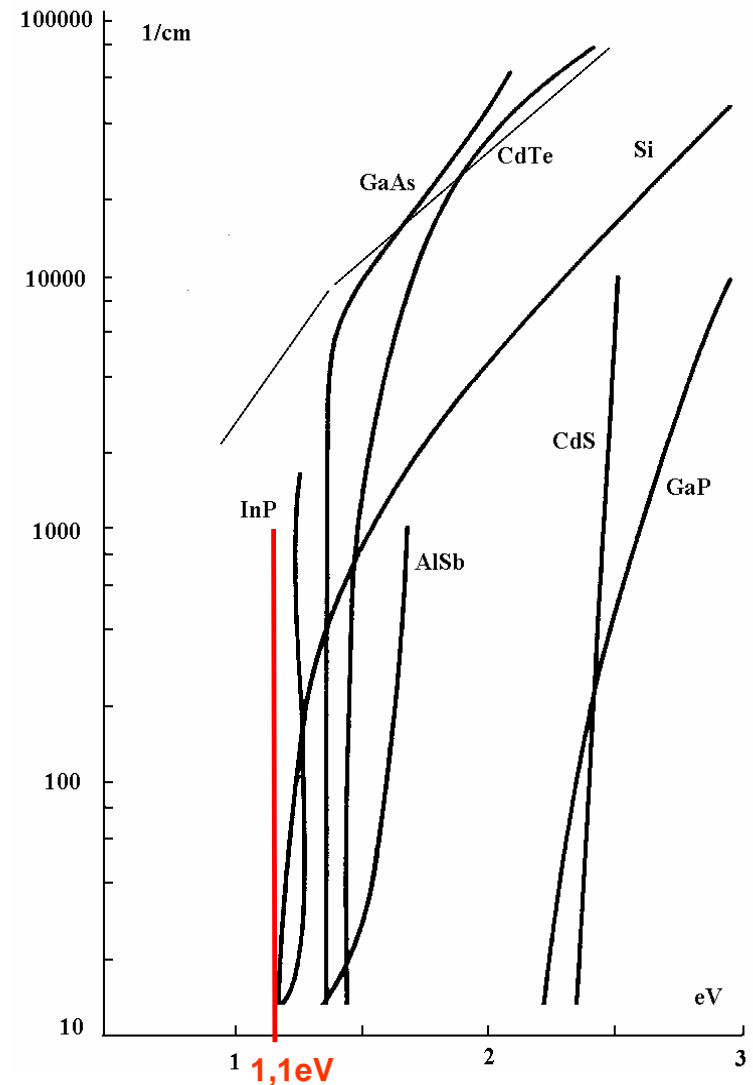


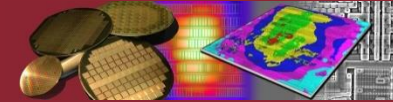
Light and semiconductor interaction

$$dI_f = -\alpha \cdot I_f \cdot dx$$

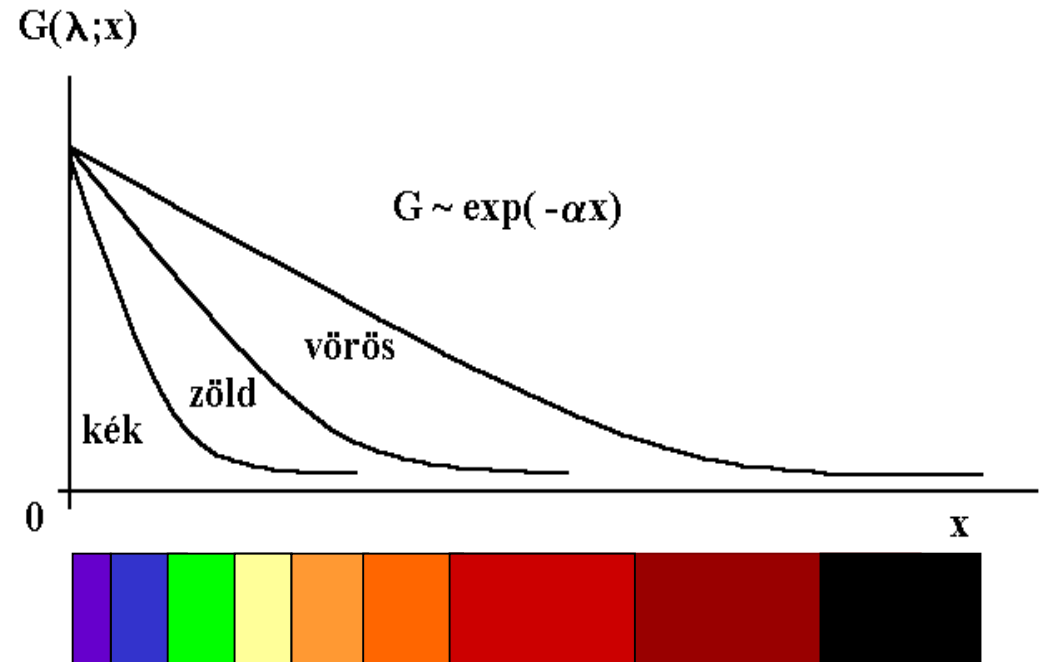
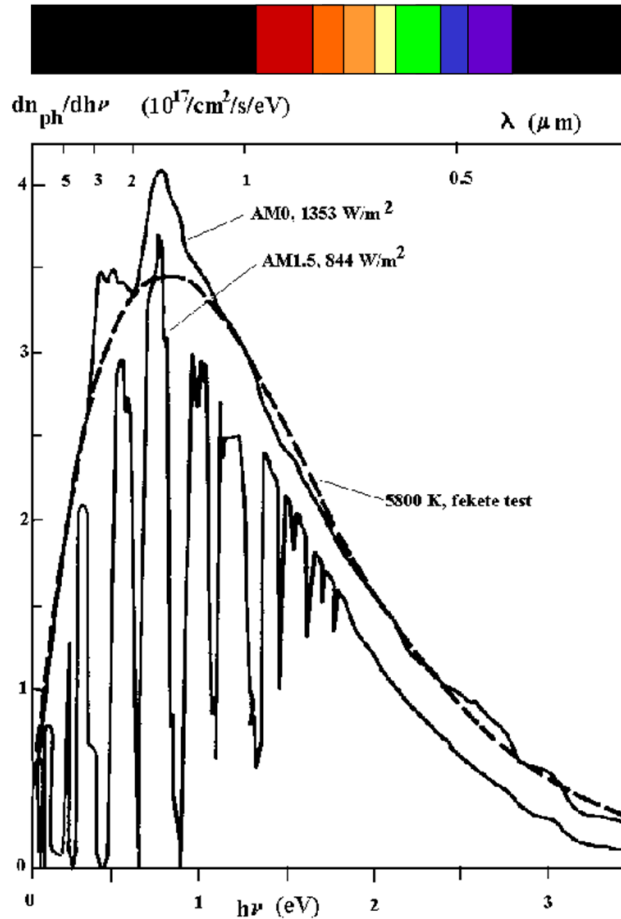


$$I_f = I_{f0} \exp(-\alpha \cdot x)$$



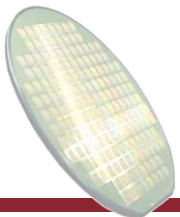


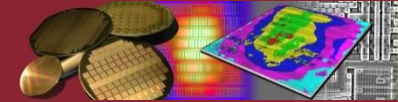
Generation rate



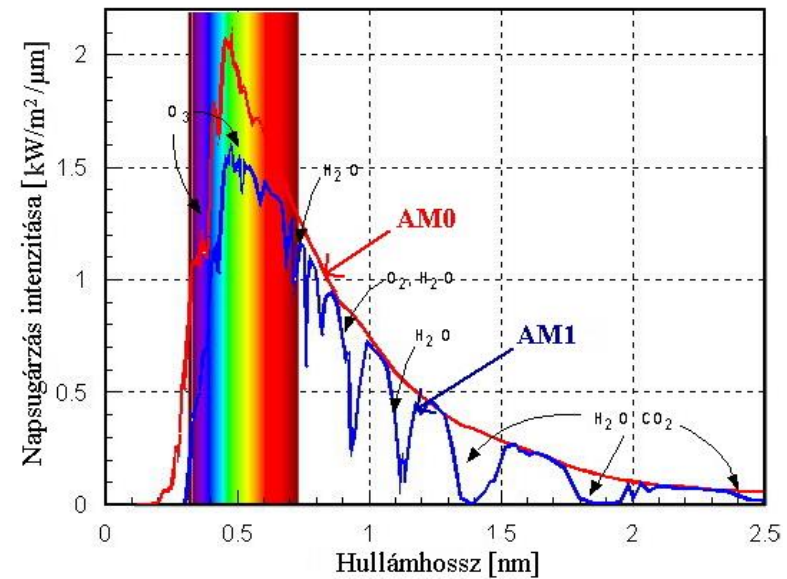
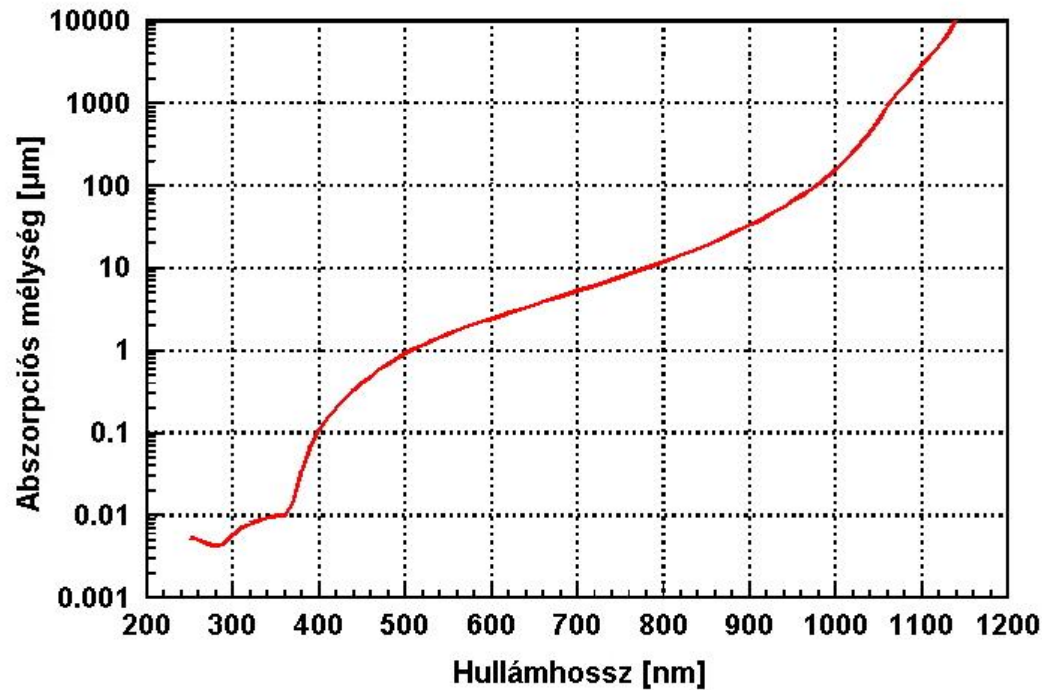
Calculation of the generation rate:

$$G(\lambda, x) = \alpha(\lambda) \cdot F(\lambda) \cdot [1 - R(\lambda)] \cdot \exp(-\alpha(\lambda) \cdot x)$$

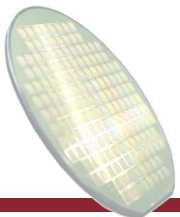




Absorption depth



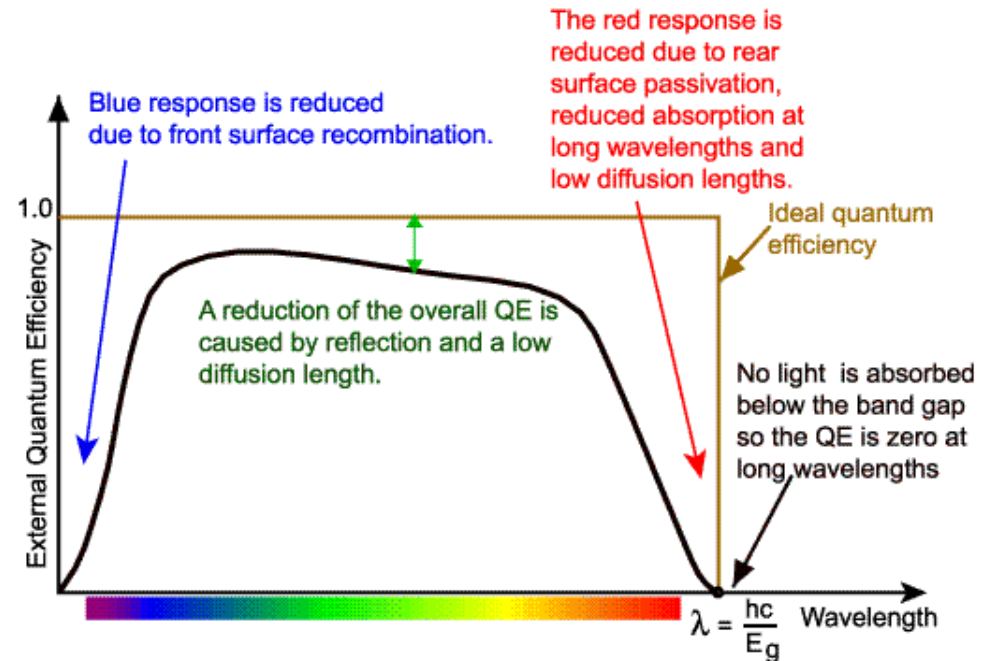
- ▶ UV and blue light have a high absorption coefficient → absorbed at the surface
- ▶ NIR wavelengths have a lower absorption coefficient → absorbed in the depth of the material





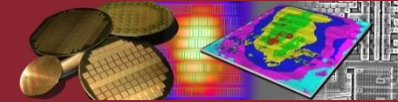
Quantum efficiency

- ▶ The ratio of the number of extracted electrons and the number of irradiated photons
- ▶ Due to reflexion there is a difference between external (EQE) and internal (IQE) quantum efficiency
- ▶ The sum of all the extracted electrons is the short circuit current that almost equals the photocurrent
- ▶ It is complicated to measure the number of photons



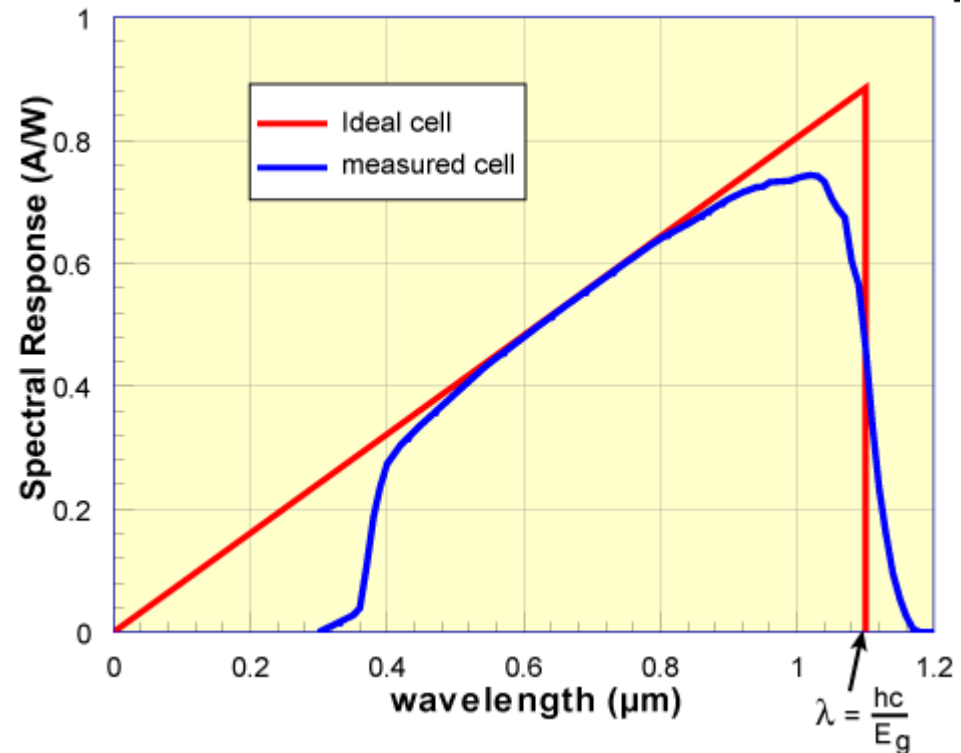
$$I_L = q \int_{(\lambda)} F(\lambda) \cdot [1 - R(\lambda)] \cdot IQE(\lambda) d\lambda$$





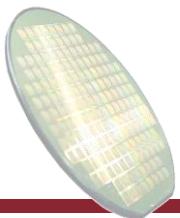
Spectral response

- ▶ A generált fotoáram és az adott hullámhosszú fény teljesítményének hányadosa, adott felületen
- ▶ A napelem rétegszerkezetének vizsgálatára alkalmas
- ▶ Technológia ismeretében az esetleges hibák kideríthetők (rossz felületi passziválás, BSF réteg)



$$\text{SR} = \frac{J_z}{P_{\text{fény}}} = \frac{I_z}{A \cdot P_{\text{fény}}}$$

$$\text{SR}(\lambda) = \frac{q \cdot \lambda}{h \cdot c} \cdot \text{QE}(\lambda) = 0,808 \cdot \lambda \cdot \text{QE}(\lambda)$$

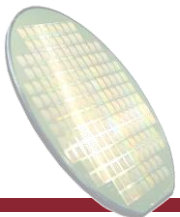


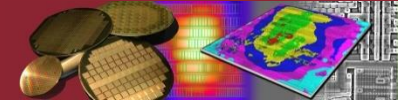


Spectral response – what is it for?

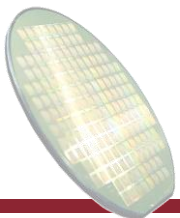
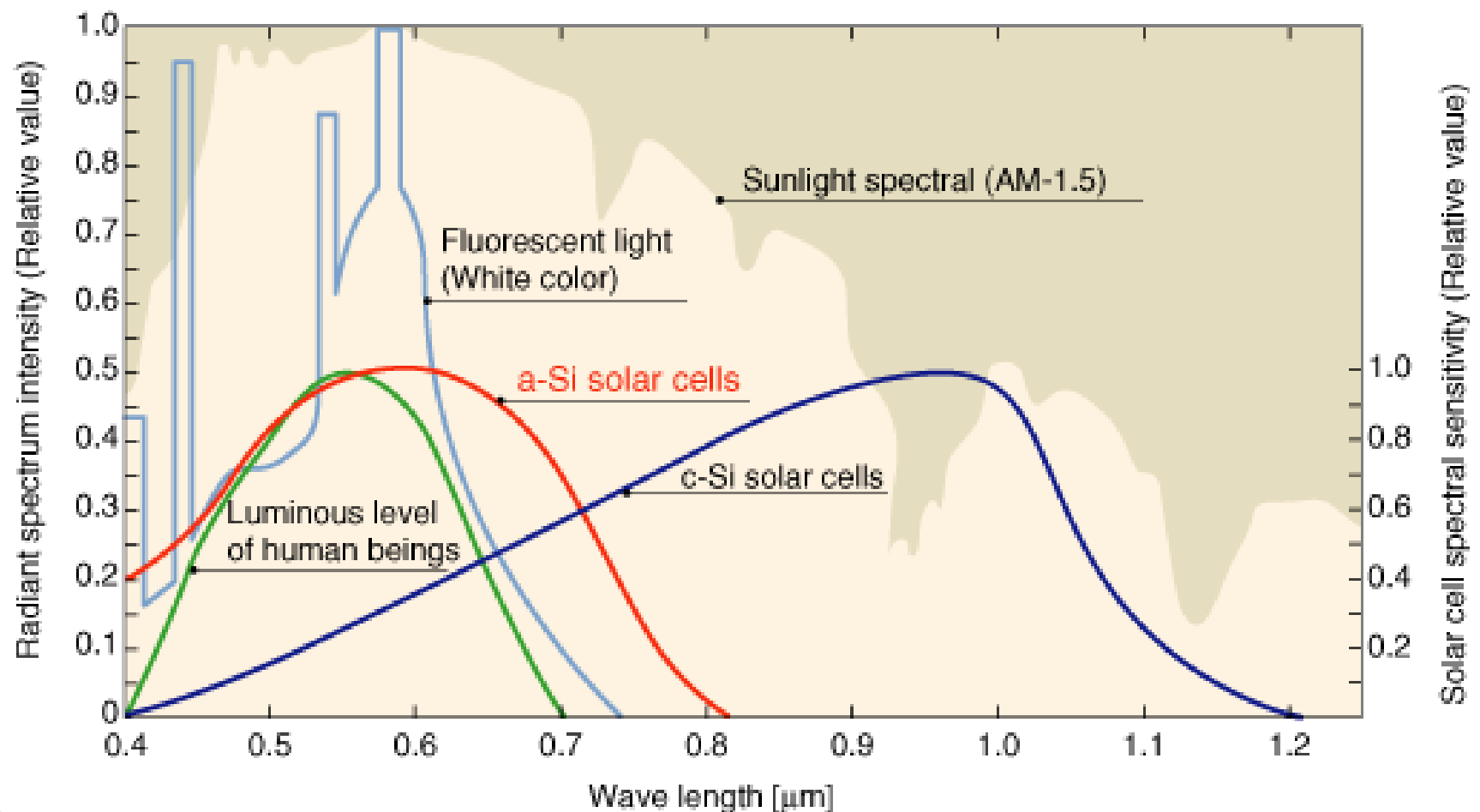
1. It is a „footprint” of the technology! (It shows the nature and location of the problems.)
2. If the spectral response is known, than the response for a given light source can be calculated:

$$J_L = q \int_0^{\lambda_m} F(\lambda) [1 - R(\lambda)] SR(\lambda) d\lambda$$





Spectral response





EFFICIENCY LIMITS AND OPERATIONAL CONDITIONS

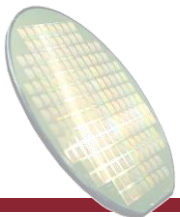




Loss factors

- ▶ Photons with lower energy than the band gap
- ▶ Above bandgap photon energy
- ▶ Broad solar spectrum
- ▶ Voltage reduction: due to its structure a solar cell can not produce an open circuit voltage of 1,12 V as its band gap would suggest, but only ca. 0,6-0,7 V
- ▶ Fill Factor: the I-V curve is not „square”, thus we have losses due to the exponential characterisic of the p-n junction: the diode is partially open at the maximum power point.

$$\eta_{max} = 29 \% \text{ (for silicon, AM 1,5 solar spectrum)}$$

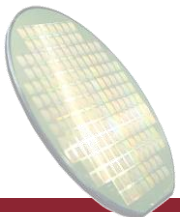
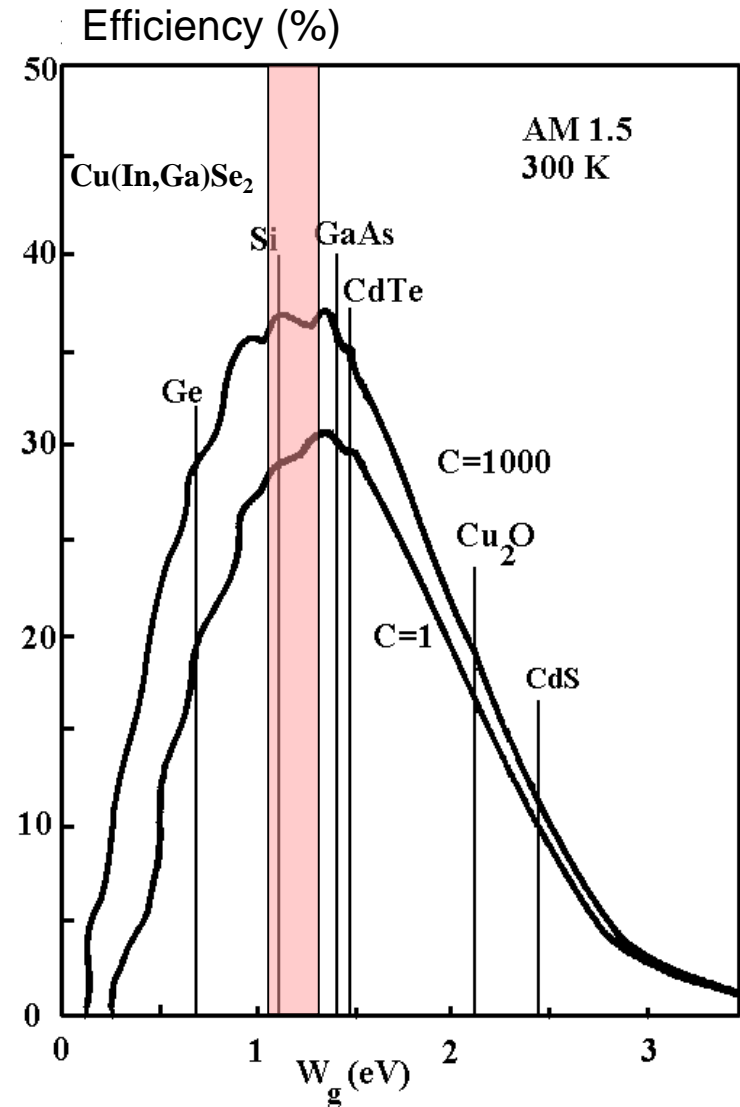




Choosing the semiconductor material

Optimal material

- ▶ AM1.5 Earth conditions
- ▶ Without concentration,
- ▶ 1000x concentration
- ▶ Theoretical limit for the conversion efficiency as function of the energy gap (Shockley-Queisser Limit)





Effect of illumination

Open-circuit condition ($I=0$)

$$U_0 = U_T \ln \left(1 + \frac{I_L}{I_S} \right) \cong U_T \ln \frac{I_L}{I_S} = U_T \ln \frac{kI_{f0}}{I_S}$$

10x-higher intensity:

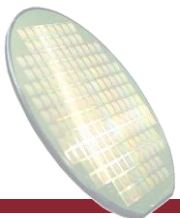
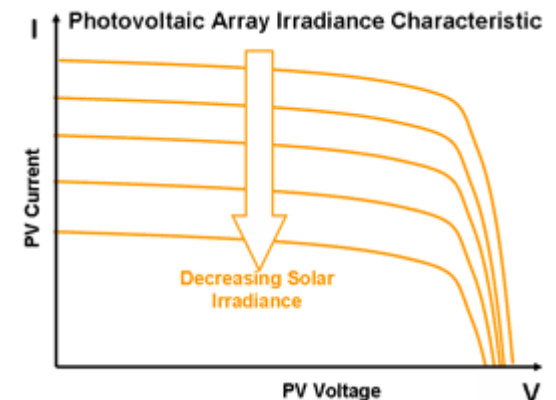
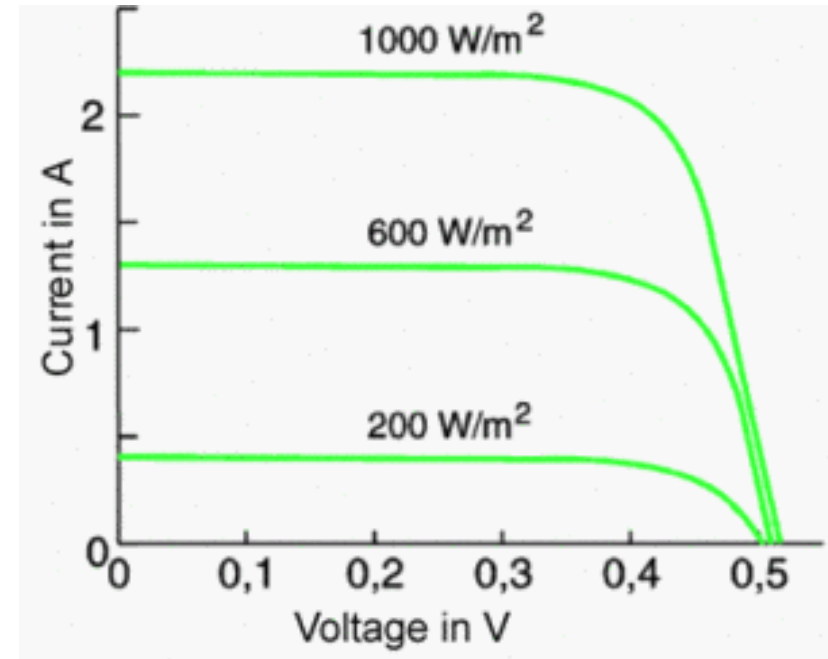
$$\Delta U = U_T \ln 10 = 60 \text{ mV}$$

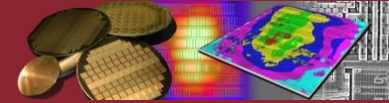
Short-circuit condition ($U=0$)

$$I_{sc} = -I_L = kI_{f0}$$

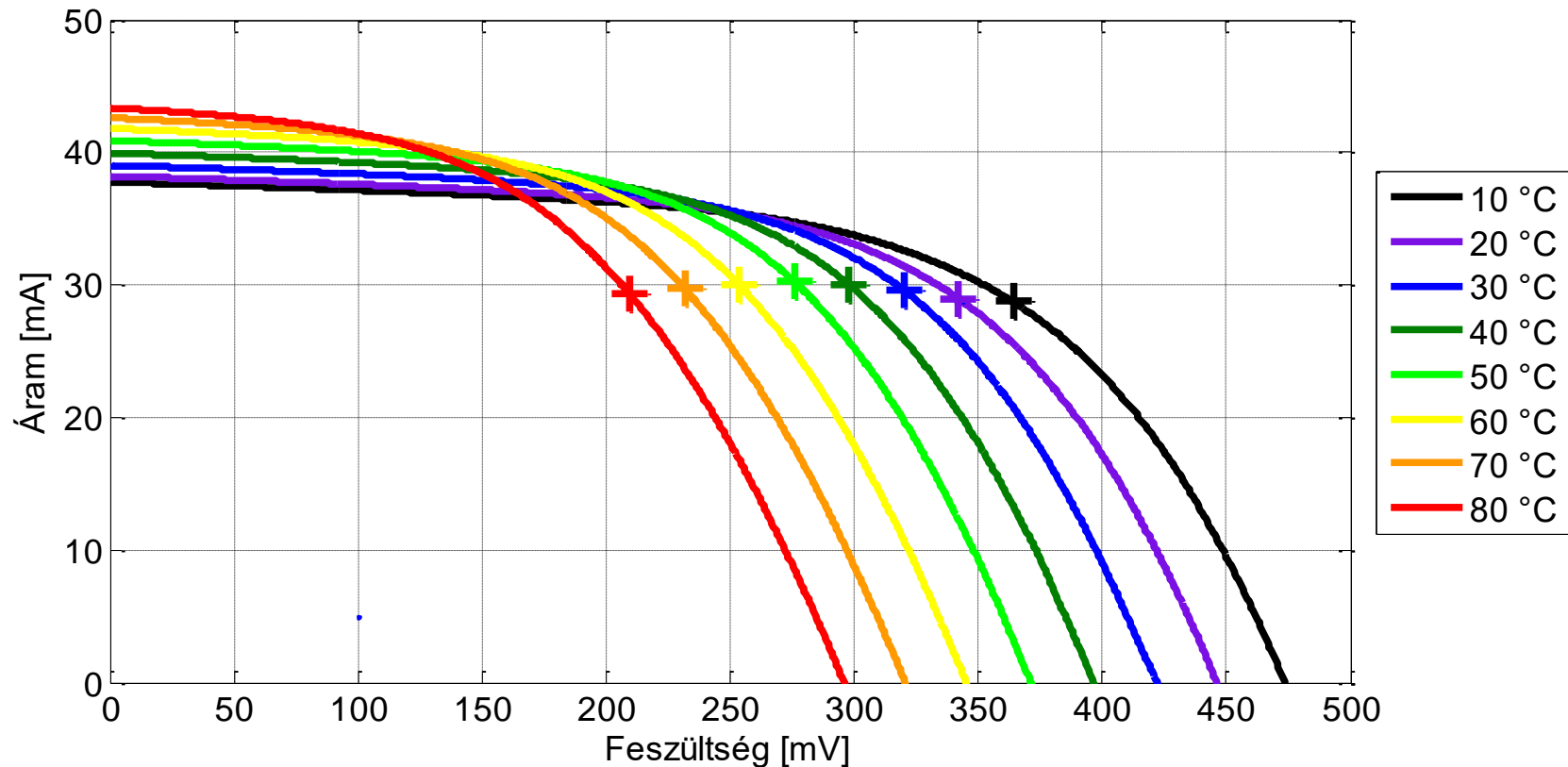
10x- higher intensity: $I_{sc,10} = 10 \cdot I_{sc}$

I_{f0} – photon flux (incoming photons/ sec)



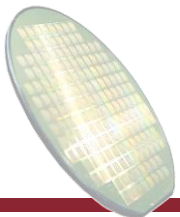


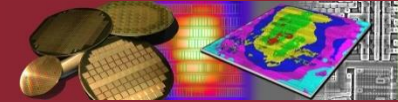
Effect of temperature



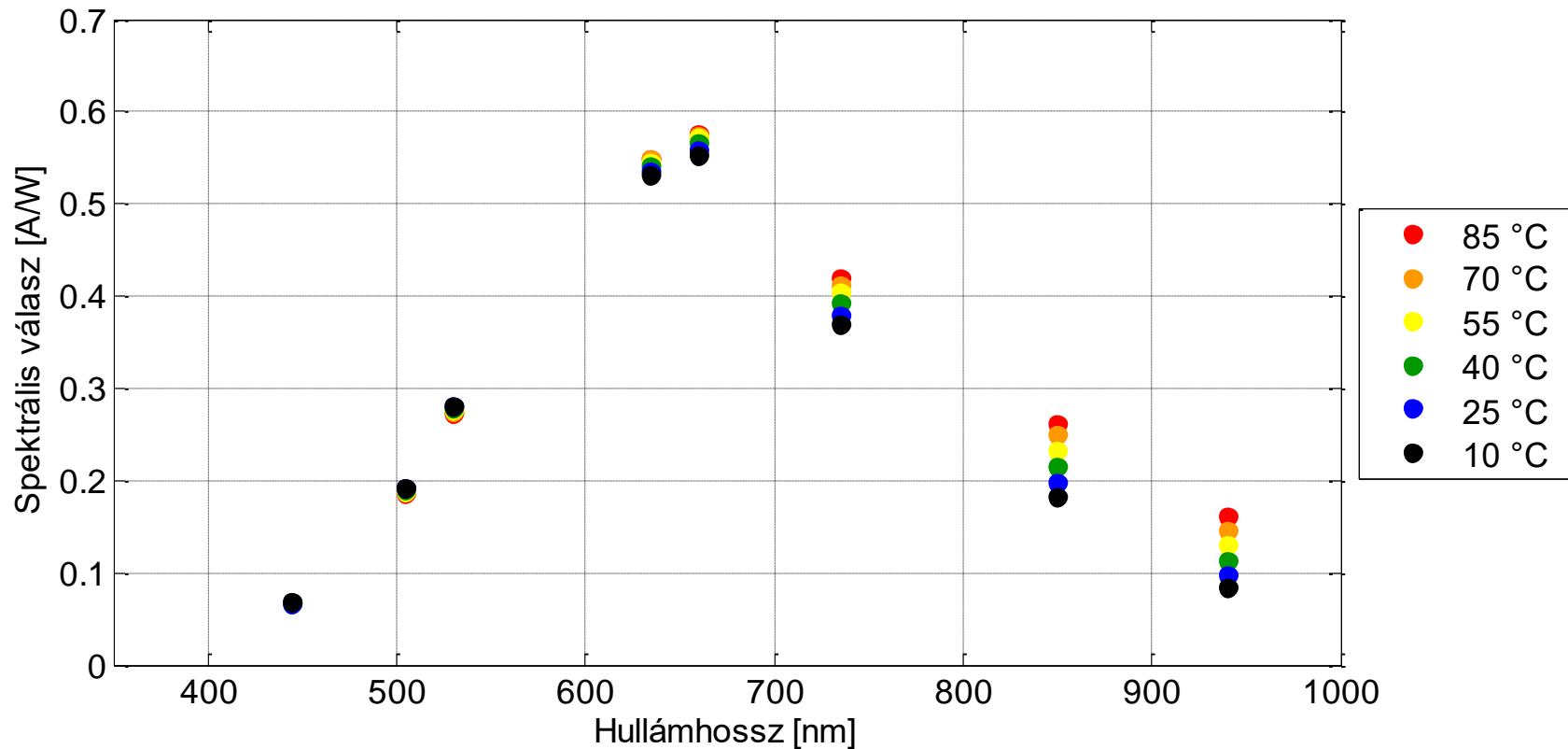
$$\frac{dI_{sc}}{dT} \approx 0,1..0,2 \text{ \%}/^{\circ}\text{C}$$

$$\frac{dU_{oc}}{dT} \approx 2 \text{ mV}/^{\circ}\text{C}$$



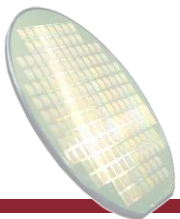


Effect of temperature on the spectral response



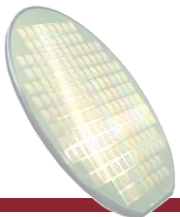
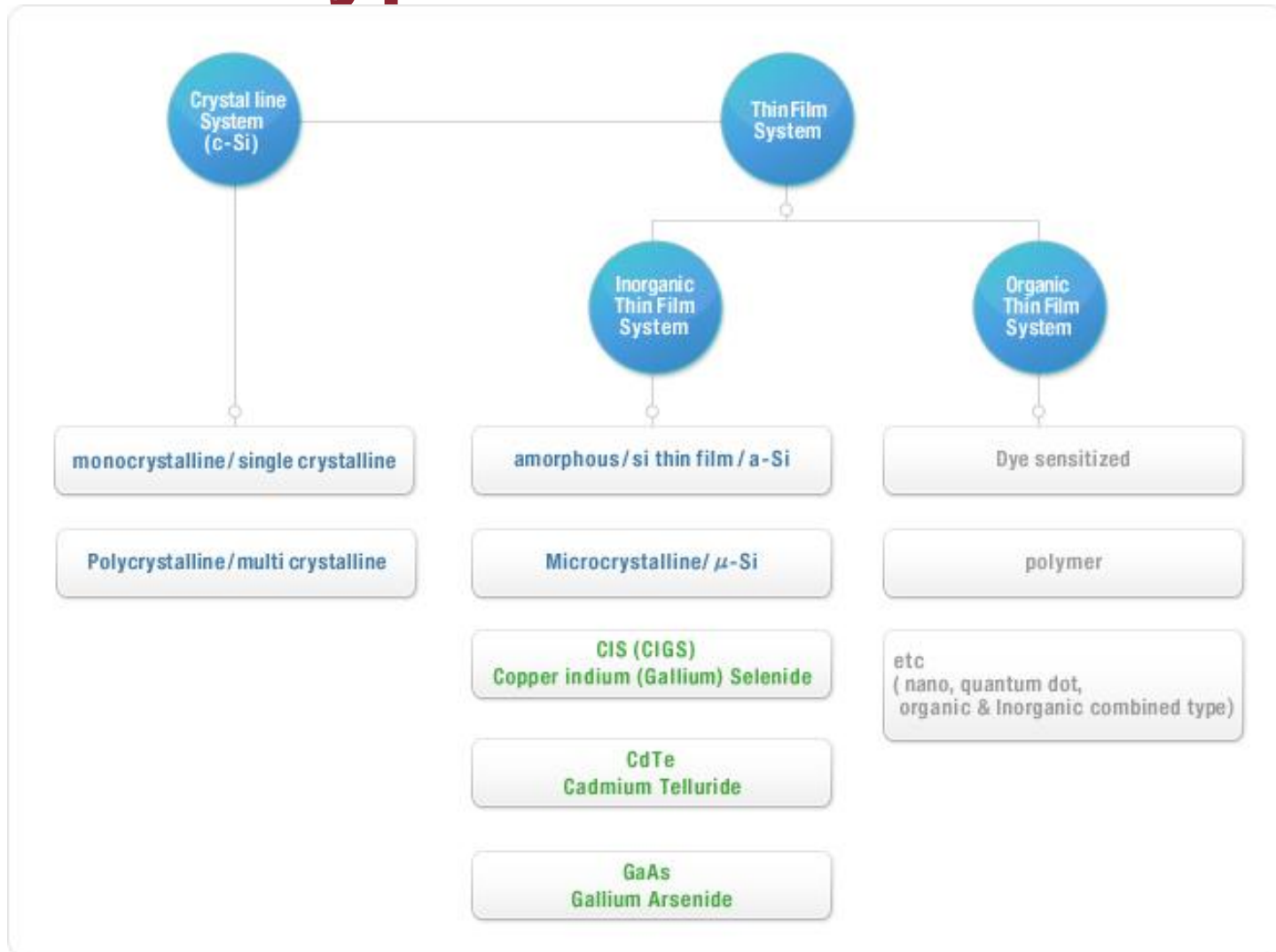


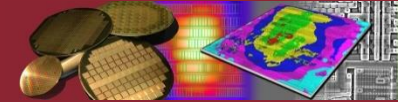
TYPES OF SOLAR CELLS





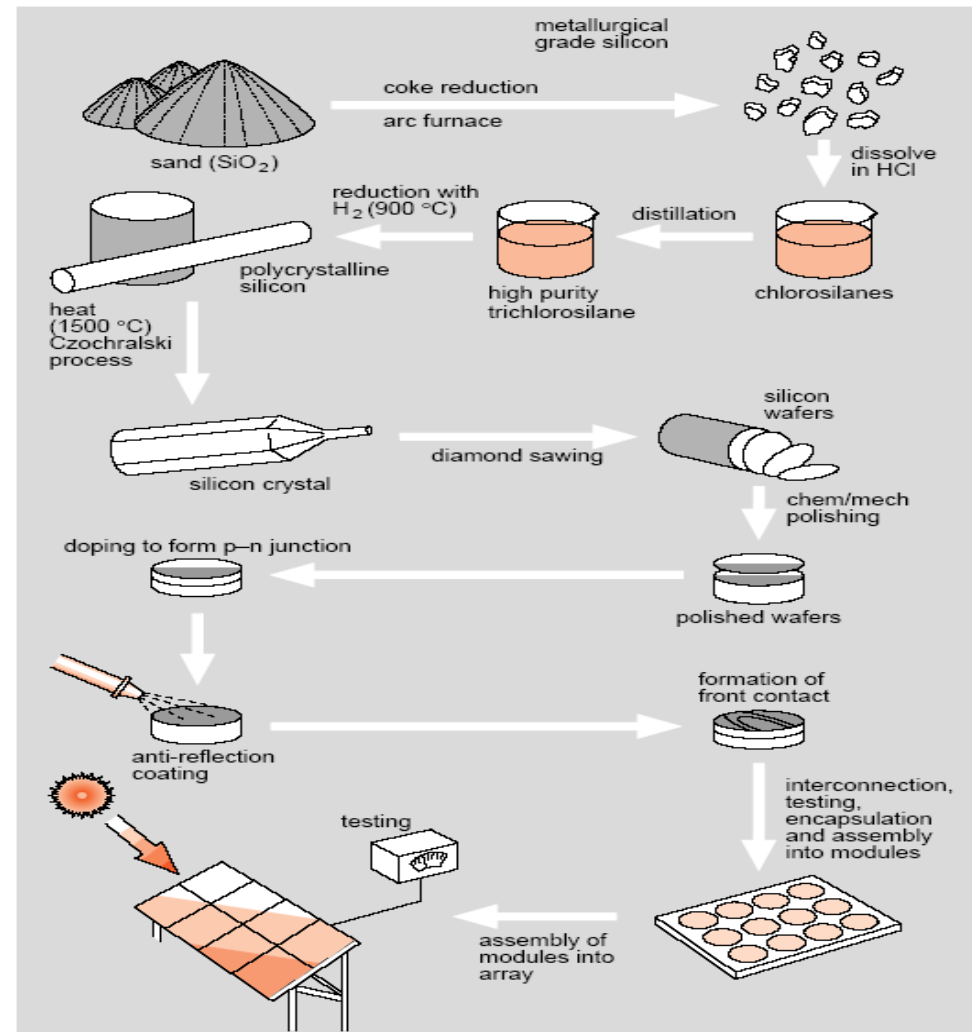
Solar cell types





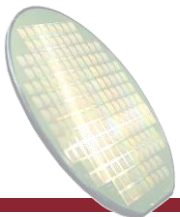
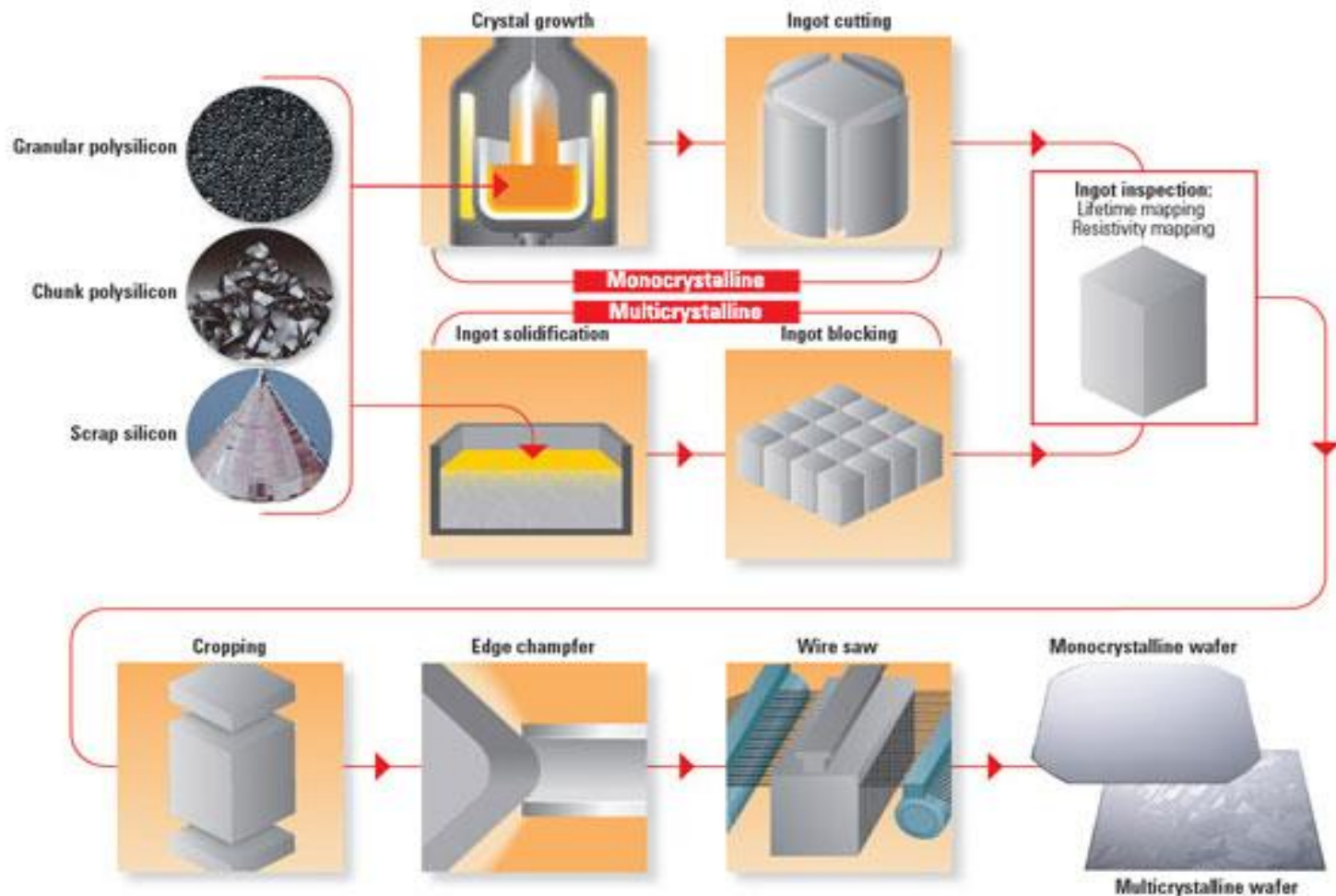
Process steps of monocrystalline solar cells

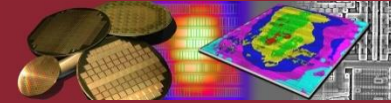
- Sand (SiO_2)
- Metallurgic Si
- Chlorsilanes (for example SiHCl_3)
- High purity chlorsilan
- Polycrystalline Si bulk
- Single crystal growth
- Slicing of the bulk (diamond saw)
- Polishing of the surface
- Adalékolás
- ARC layer
- Contact layer
- Modul assembly and testing



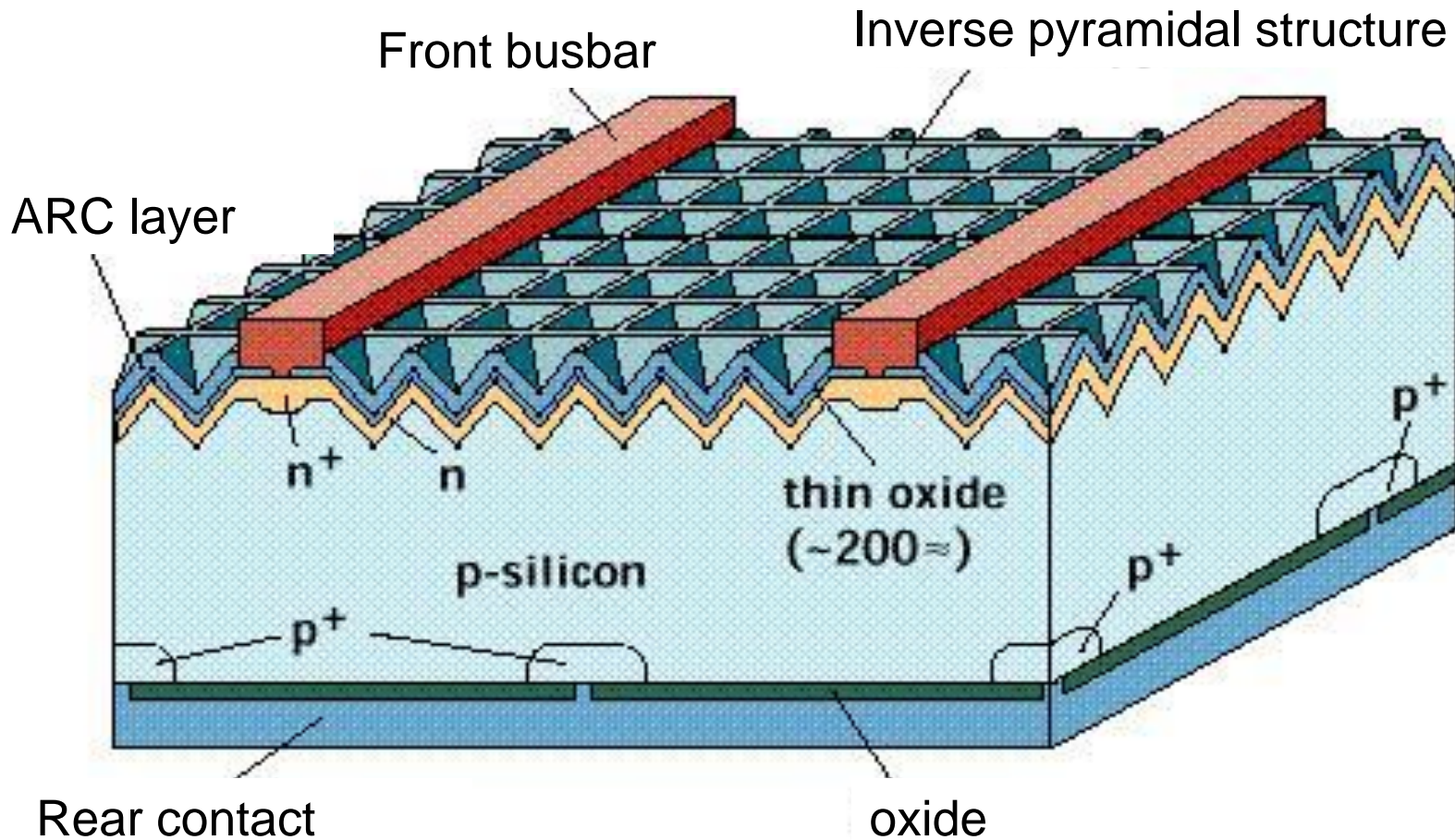


Crystalline wafer production

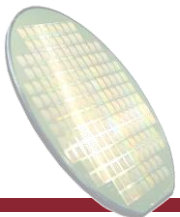


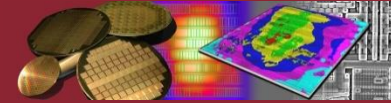


PEARL (passivated emitter and rear locally) cella

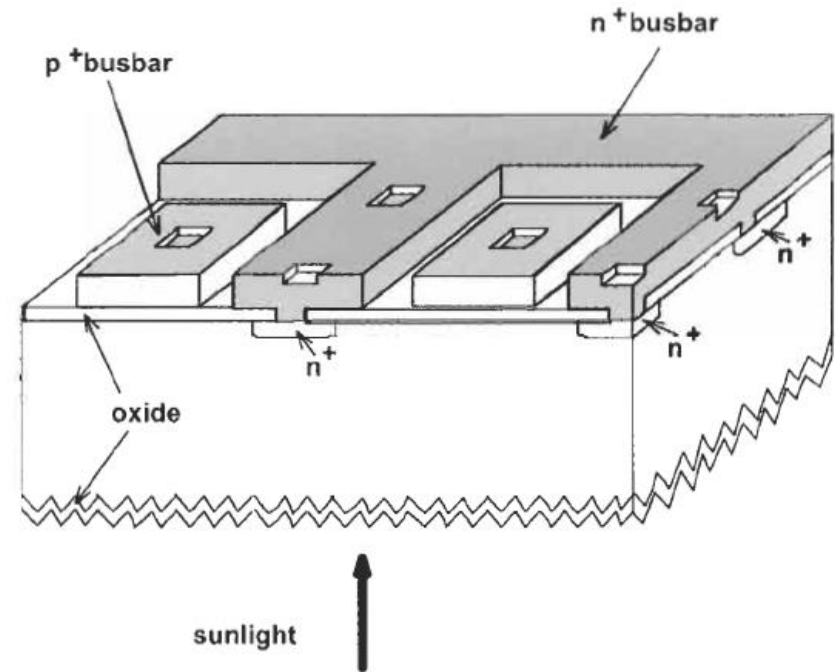
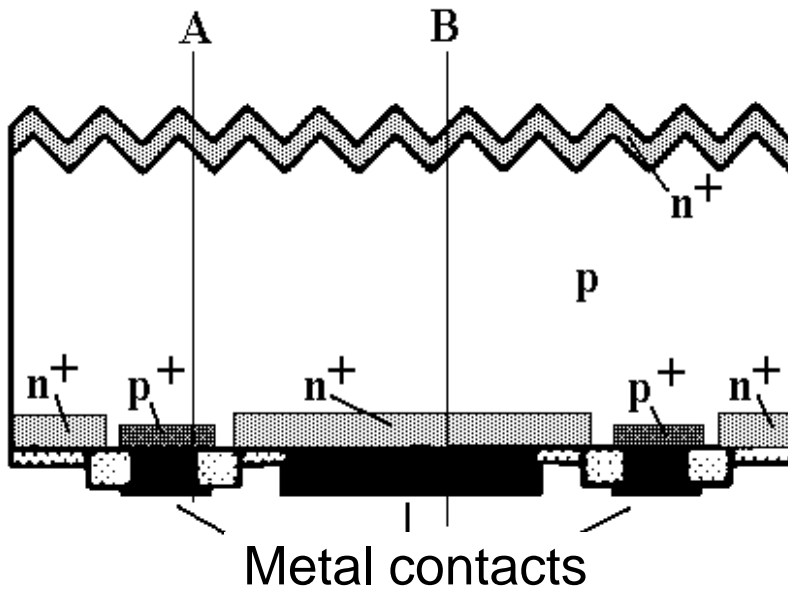


24% efficiency

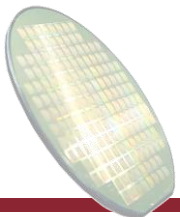


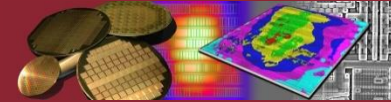


Interdigitated Back contact cells

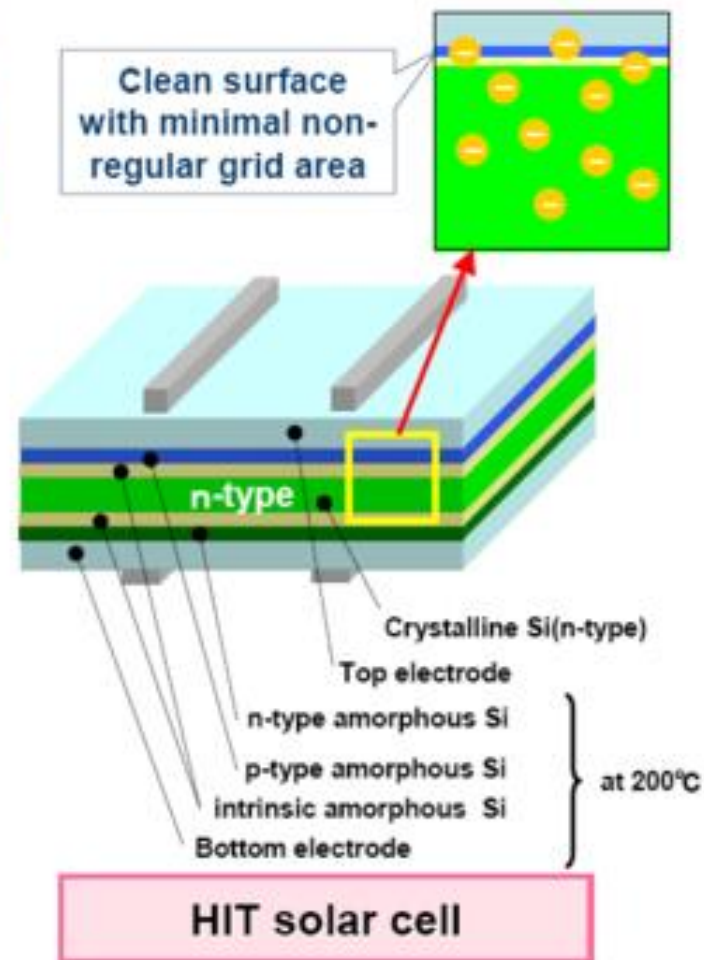
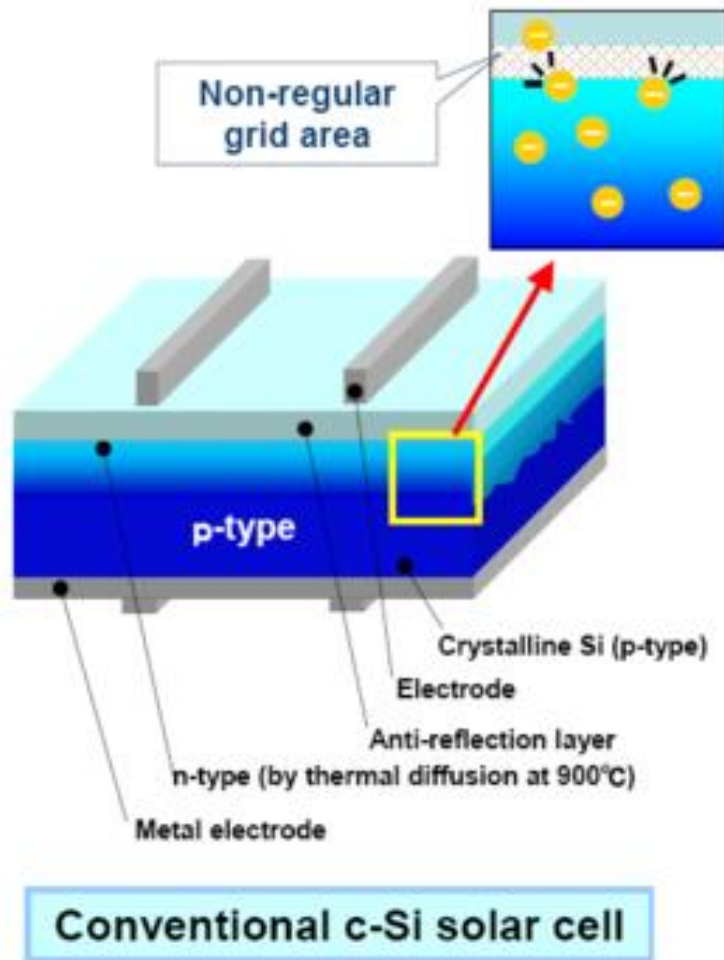


24% efficiency



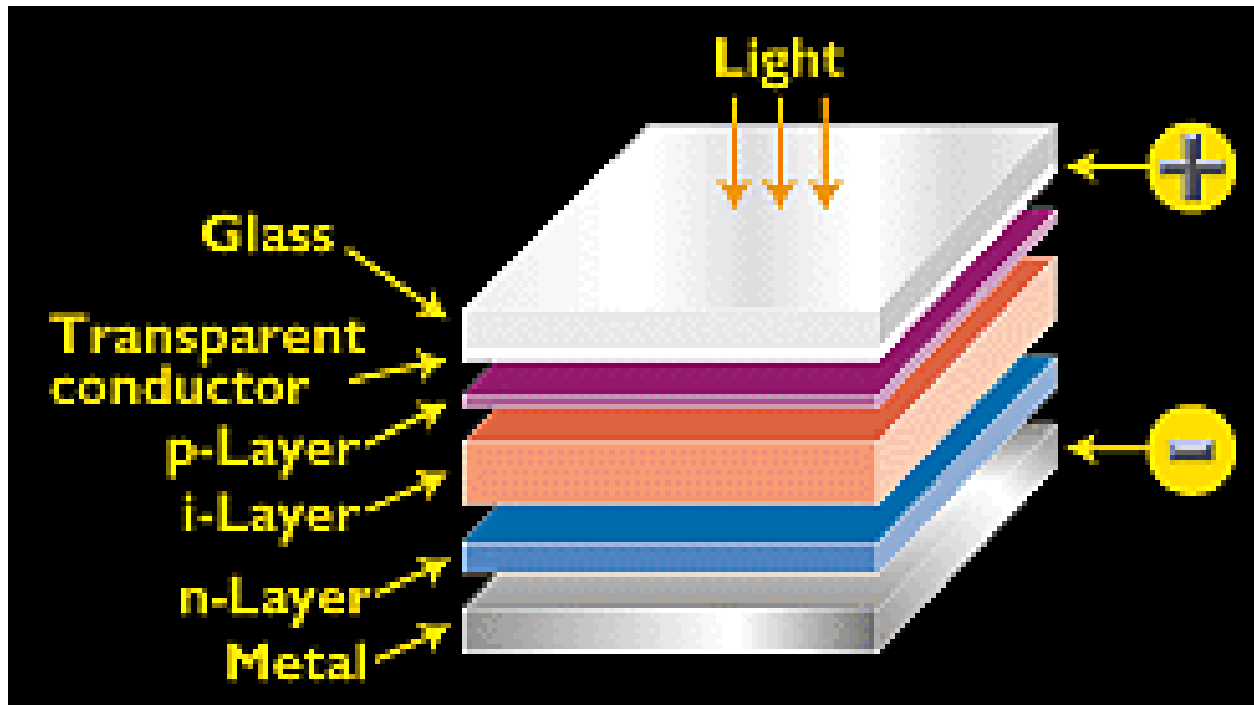


HIT cella (Sanyo)

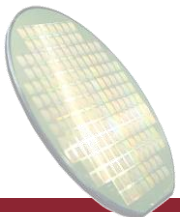


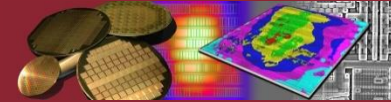


Amorphous Si solar cell (a-Si)

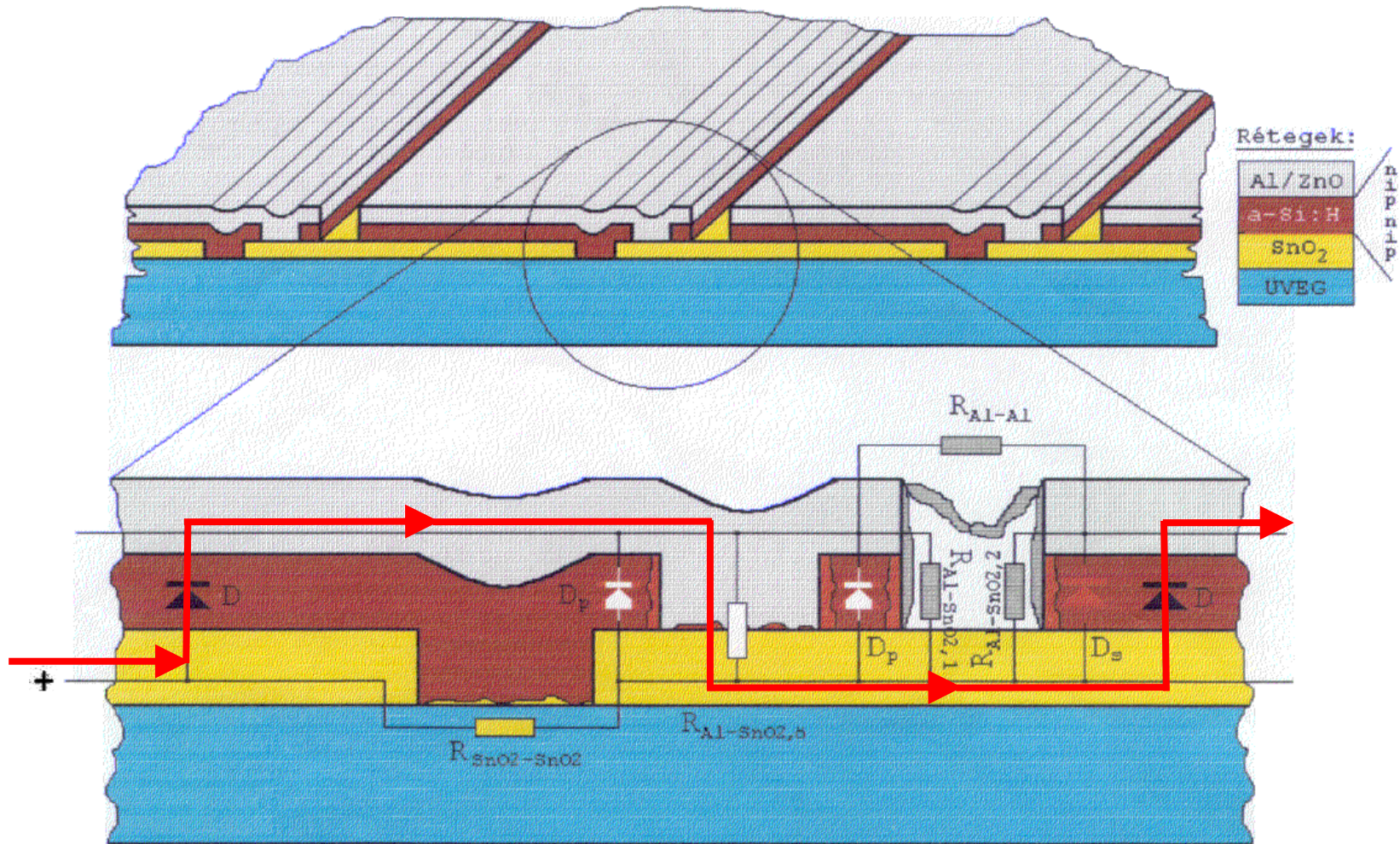


- ▶ ultra thin ($0,008 \mu\text{m}$) p^+ layer
- ▶ intrinsic layer ($0,5 - 1 \mu\text{m}$)
- ▶ thin ($0,02 \mu\text{m}$) n^+ layer



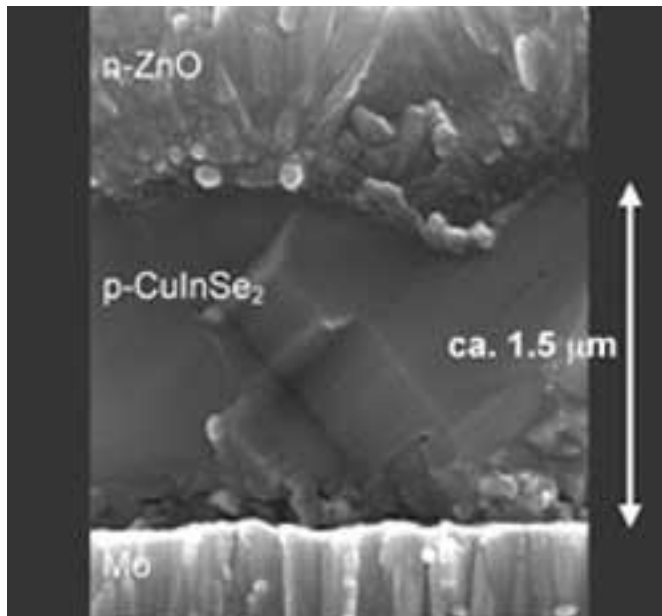


Amorphous Si solar cell (a-Si)





CIS (copper indium diselenid)



Cella cross-sectional view

Window Layer 0.1 μm ZnO:Al

Adaption Layer

Cadmium Sulphide CdS 0.05 μm

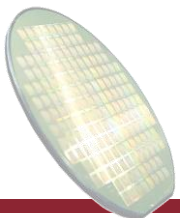
Absorber layer

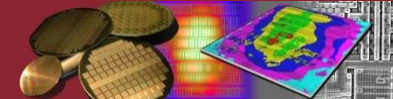
Copper Indium Diselenide Cu In Se₂
2 μm

Back contact 0.5 μm - molybdenum

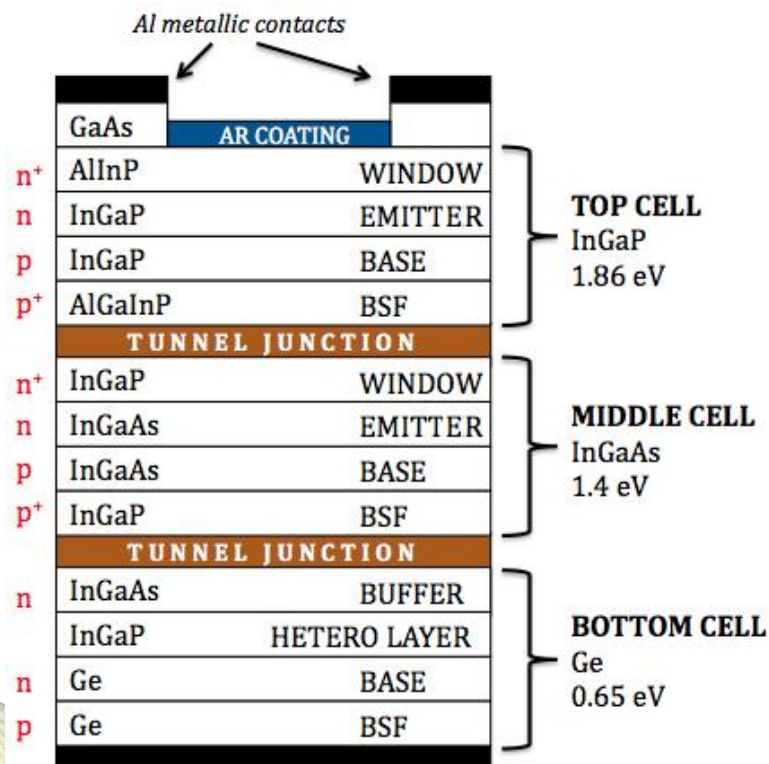
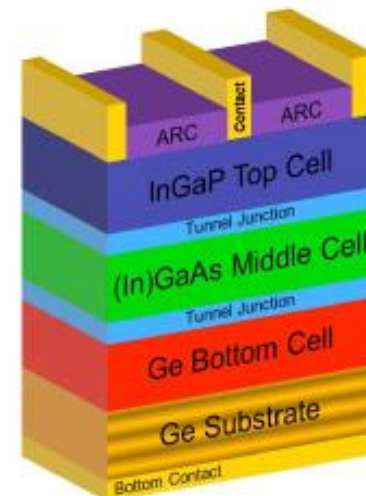
Glass substrate 2 - 4 mm

CIS stucture

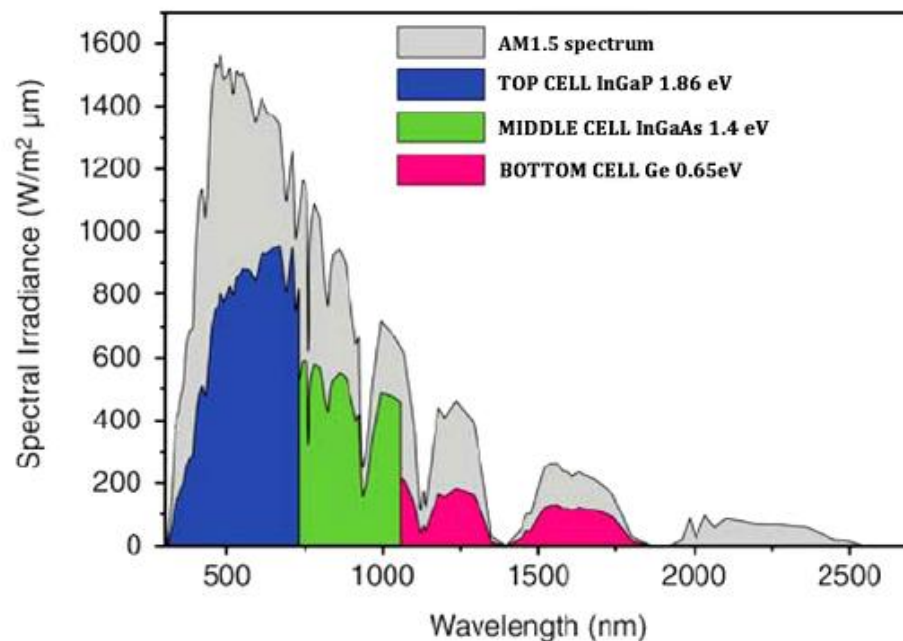




Multijunction solar cells



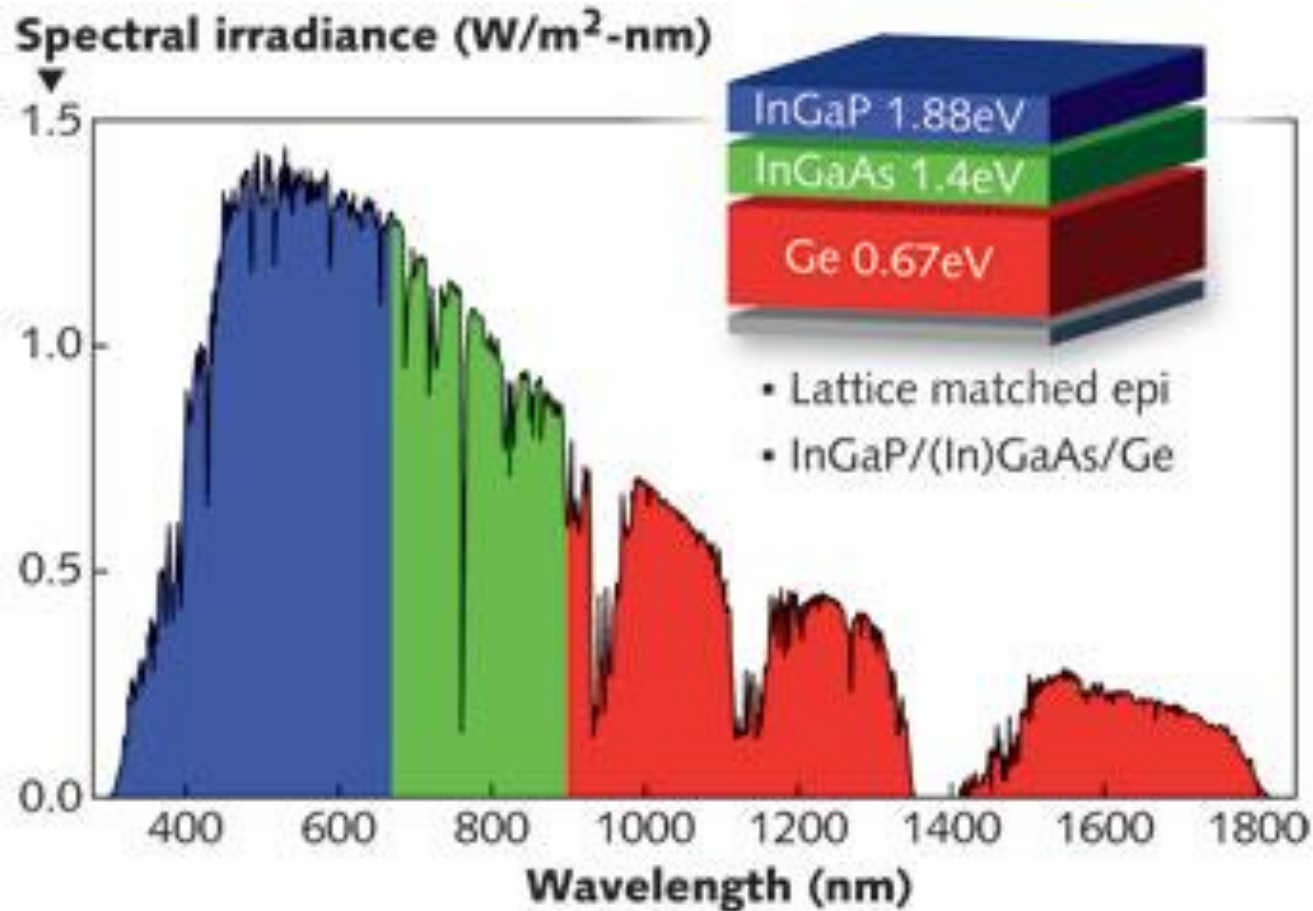
(a)

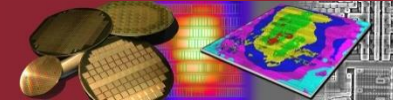


(b)



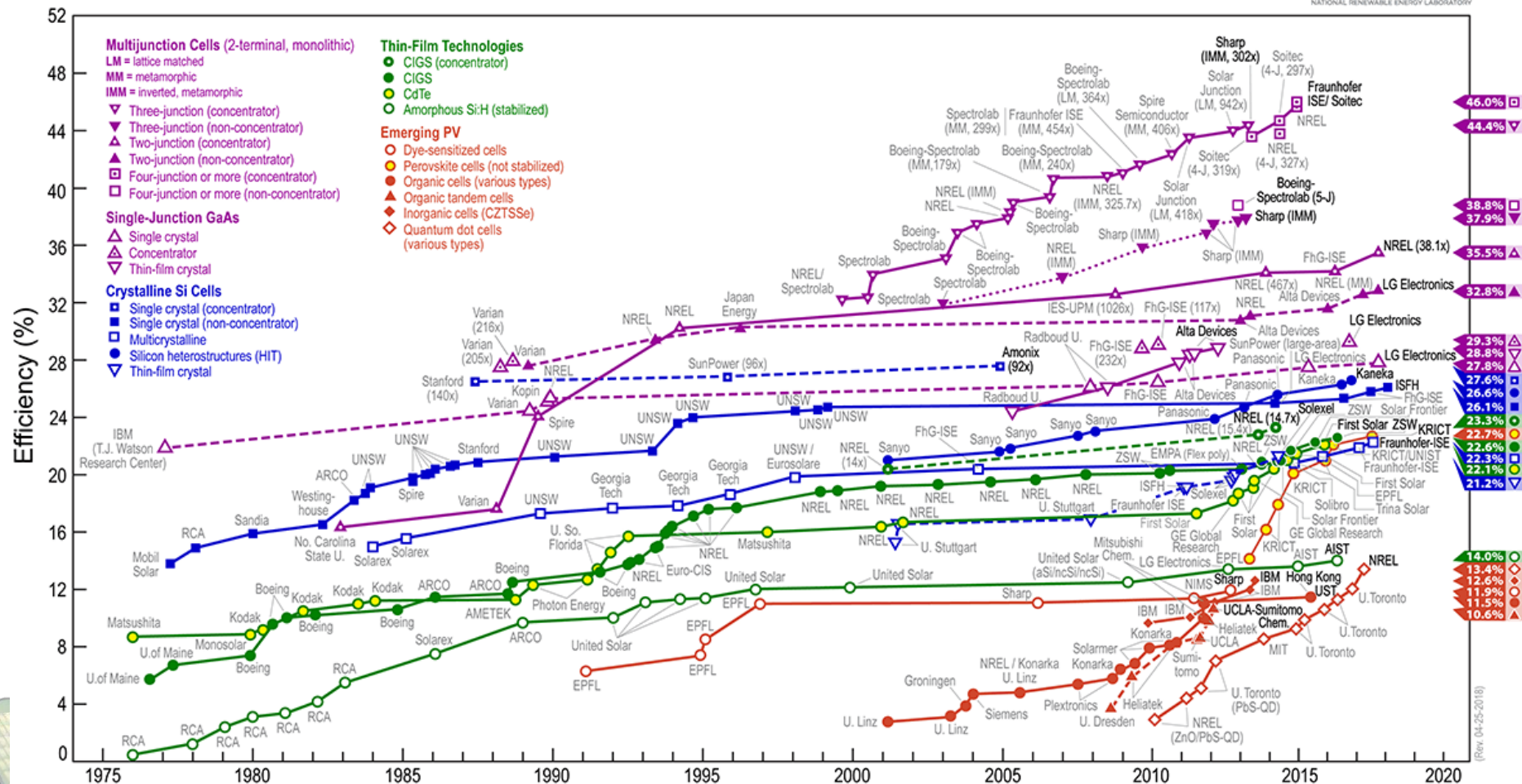
Multijunction solar cells





NREL efficiency chart

Best Research-Cell Efficiencies





If you want to know more...

- ▶ Course: Solar Cells and Renewable Energy sources
 - 4 credits
 - 2 lectures (90 min) a week
 - BME VIEEAV99
 - <https://portal.vik.bme.hu/kepzes/targyak/VIEEAV99/en/>

